(12) **United States Patent**
Kageyama et al.

(10) **Patent No.: US 9,627,344 B2**
(45) **Date of Patent: Apr. 18, 2017**

(54) **SEMICONDUCTOR DEVICE**

(71) Applicant: **ROHM CO., LTD.**, Kyoto (JP)

(72) Inventors: **Satoshi Kageyama**, Kyoto (JP); **Isamu Nishimura**, Kyoto (JP)

(73) Assignee: **ROHM CO., LTD.**, Kyoto (JP)

(*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.

(21) Appl. No.: **14/243,245**

(22) Filed: **Apr. 2, 2014**

(65) **Prior Publication Data**

US 2014/0299990 A1 Oct. 9, 2014

(30) **Foreign Application Priority Data**

Apr. 4, 2013 (JP) 2013-078758
Apr. 4, 2013 (JP) 2013-078759

(51) **Int. Cl.**
H01L 23/00 (2006.01)
H01L 23/495 (2006.01)
(Continued)

(52) **U.S. Cl.**
CPC ***H01L 24/45*** (2013.01); ***H01L 23/53238*** (2013.01); ***H01L 24/03*** (2013.01); ***H01L 24/05*** (2013.01); ***H01L 24/48*** (2013.01); ***H01L 24/85*** (2013.01); *H01L 23/3121* (2013.01); *H01L 23/4952* (2013.01); *H01L 23/49548* (2013.01); *H01L 23/49582* (2013.01); *H01L 23/53223* (2013.01); *H01L 24/73* (2013.01); *H01L 2224/04026* (2013.01); *H01L 2224/04042* (2013.01); *H01L 2224/05147* (2013.01); *H01L 2224/05155* (2013.01); *H01L 2224/05164* (2013.01); *H01L 2224/05166* (2013.01);
(Continued)

(58) **Field of Classification Search**
CPC ... H01L 24/45; H01L 24/85; H01L 23/53238; H01L 24/48; H01L 24/05; H01L 24/03; H01L 23/3121; H01L 24/73; H01L 23/49548; H01L 23/4952; H01L 23/49582; H01L 23/53223
See application file for complete search history.

(56) **References Cited**

U.S. PATENT DOCUMENTS

4,572,925 A * 2/1986 Scarlett 174/257
5,360,988 A 11/1994 Uda et al.
(Continued)

FOREIGN PATENT DOCUMENTS

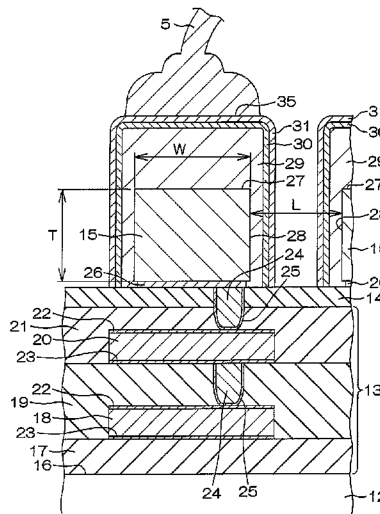
JP 2001-319946 A 11/2001
JP 2002-033393 A 1/2002
(Continued)

Primary Examiner — Jarrett Stark
(74) *Attorney, Agent, or Firm* — Rabin & Berdo, P.C.

(57) **ABSTRACT**

The semiconductor device of the present invention includes an insulating layer, a copper wiring for wire connection formed on the insulating layer, a shock absorbing layer formed on an upper surface of the copper wiring, the shock absorbing layer being made of a metallic material with a hardness higher than copper, a bonding layer formed on the shock absorbing layer, the bonding layer having a connection surface for a wire, and a side protecting layer covering a side surface of the copper wiring, wherein the side protecting layer has a thickness thinner than a distance from the upper surface of the copper wiring to the connection surface of the bonding layer.

18 Claims, 21 Drawing Sheets



(51) **Int. Cl.**
H01L 23/532 (2006.01)
H01L 23/31 (2006.01)

(52) **U.S. Cl.**
CPC *H01L 2224/05557* (2013.01); *H01L 2224/05558* (2013.01); *H01L 2224/05639* (2013.01); *H01L 2224/05644* (2013.01); *H01L 2224/05655* (2013.01); *H01L 2224/32245* (2013.01); *H01L 2224/45144* (2013.01); *H01L 2224/45147* (2013.01); *H01L 2224/48091* (2013.01); *H01L 2224/48247* (2013.01); *H01L 2224/48465* (2013.01); *H01L 2224/48639* (2013.01); *H01L 2224/48644* (2013.01); *H01L 2224/48655* (2013.01); *H01L 2224/48839* (2013.01); *H01L 2224/48844* (2013.01); *H01L 2224/48855* (2013.01); *H01L 2224/73265* (2013.01); *H01L 2224/83439* (2013.01); *H01L 2924/181* (2013.01)

(56) **References Cited**

U.S. PATENT DOCUMENTS

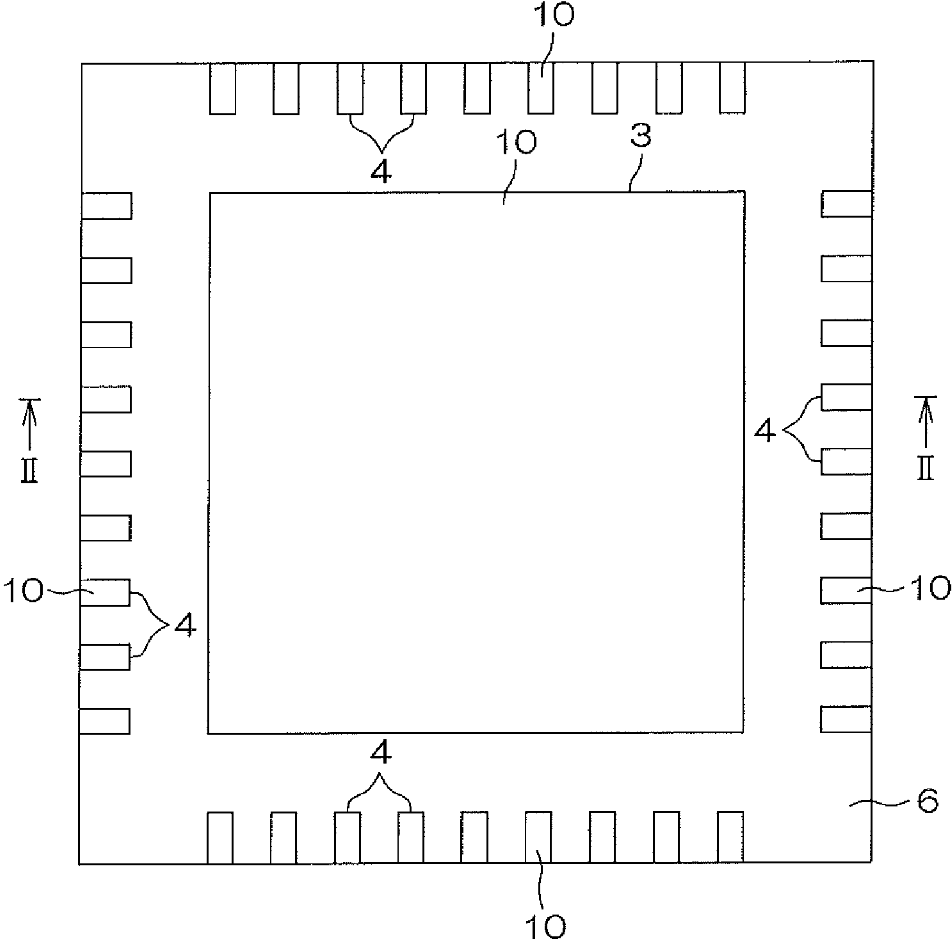
5,367,195 A * 11/1994 DiGiacomo H01L 23/49811 257/763
5,431,328 A * 7/1995 Chang et al. 228/180.22
5,519,658 A 5/1996 Uda et al.
5,855,993 A * 1/1999 Brady C23C 18/50 174/256
8,435,881 B2 * 5/2013 Choi et al. 438/612
9,006,097 B2 * 4/2015 Lu et al. 438/613
2001/0035452 A1 11/2001 Test et al.
2002/0121703 A1 * 9/2002 Toyoda H01L 21/76834 257/762
2002/0121709 A1 * 9/2002 Matsuki et al. 257/786
2004/0110367 A1 * 6/2004 Kumakura H01L 23/3171 438/613
2010/0133688 A1 * 6/2010 Shigihara H01L 24/06 257/738
2010/0164105 A1 7/2010 Onai et al.
2011/0186962 A1 8/2011 Moriyama et al.
2011/0260317 A1 * 10/2011 Lu et al. 257/737
2012/0007228 A1 * 1/2012 Lu et al. 257/692
2012/0007231 A1 * 1/2012 Chang 257/737
2012/0193787 A1 8/2012 Maitani et al.
2012/0302009 A1 * 11/2012 Sekihara H01L 24/49 438/121
2014/0061920 A1 3/2014 Hirano et al.

FOREIGN PATENT DOCUMENTS

JP 2004-047510 A 2/2004
JP 2007-208181 A 8/2007
JP 2008-503879 A 2/2008
JP 2008-112825 A 5/2008
JP 2008-258511 A 10/2008
JP 2009-505404 A 2/2009
JP 2010-171386 A 8/2010
JP 2011-222963 A 11/2011
JP 2012-160512 A 8/2012
WO WO-2006/009850 A2 1/2006
WO WO-2007/021736 A2 2/2007
WO WO 2012-176392 A1 12/2012

* cited by examiner

FIG. 1



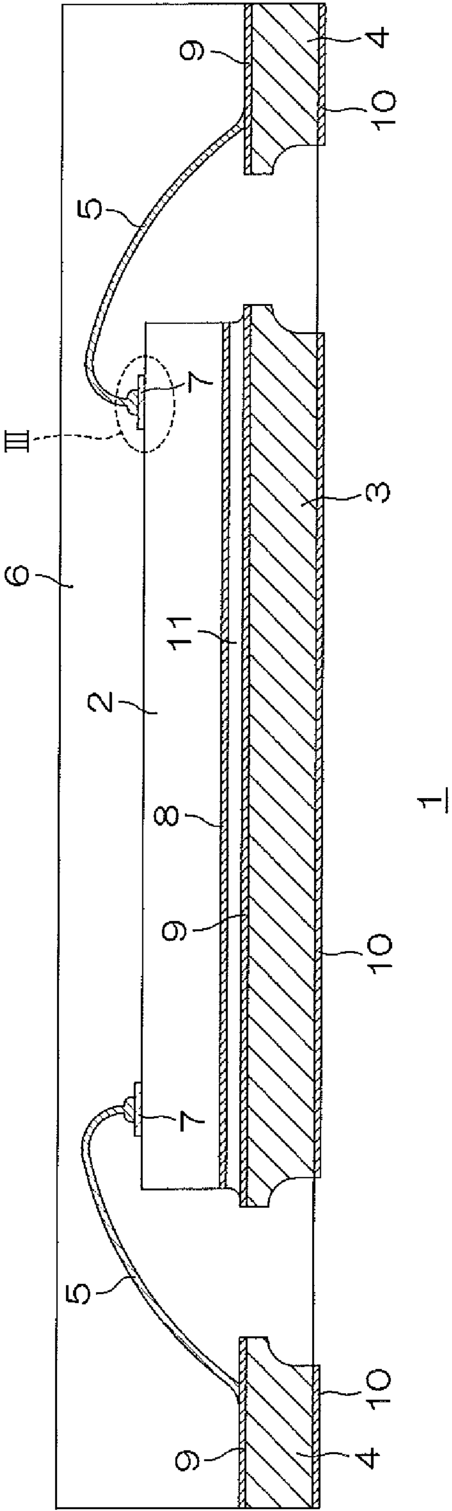


FIG. 2
1
2
3
4
5
6
7
8
9
10
11
III

FIG. 3

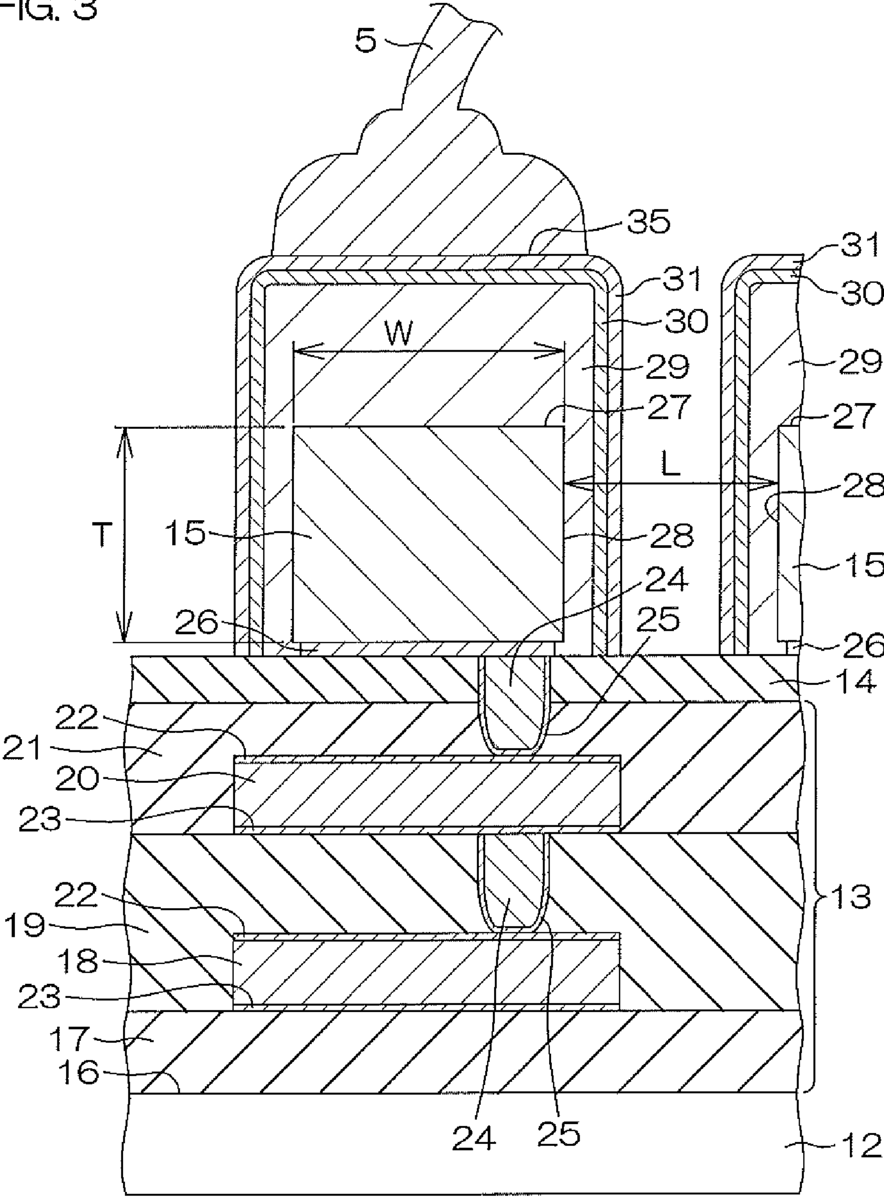


FIG. 4A

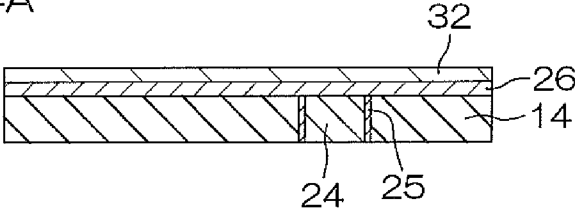


FIG. 4B

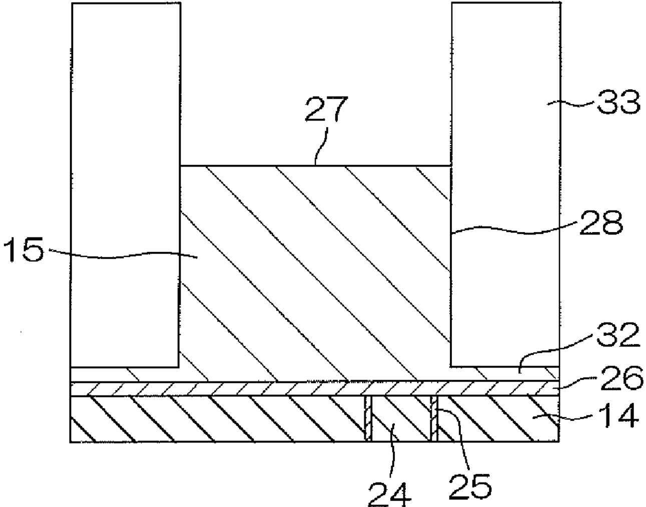


FIG. 4C

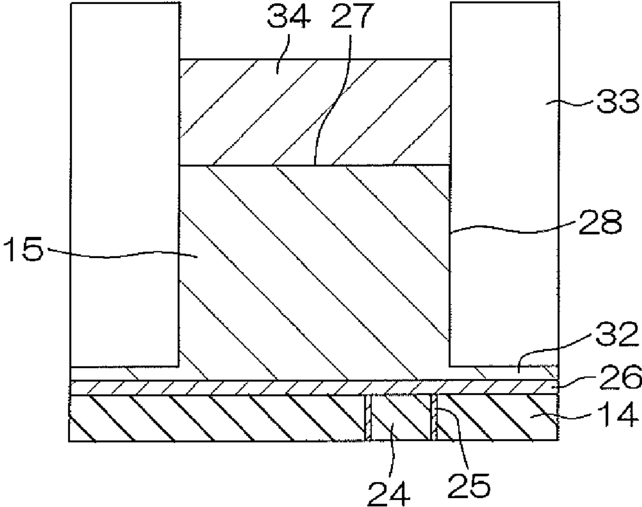


FIG. 4D

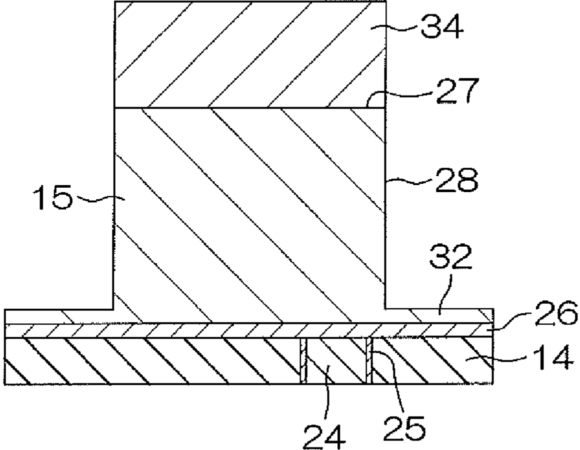


FIG. 4E

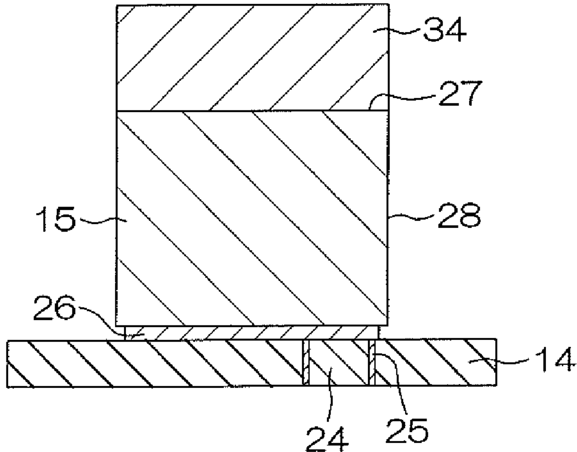


FIG. 4F

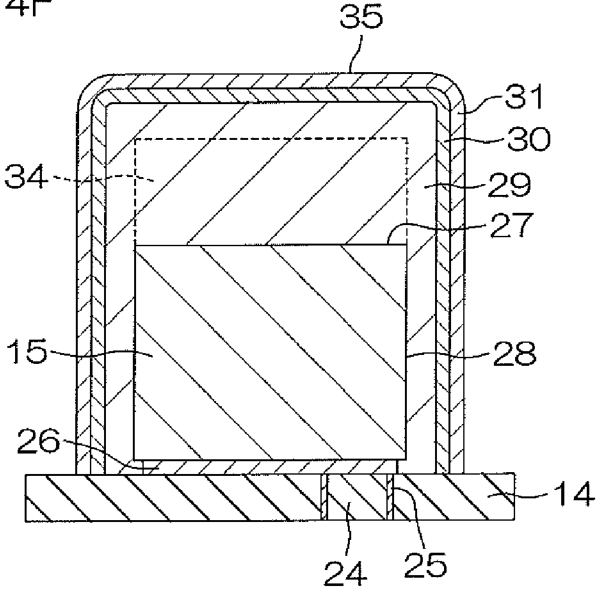


FIG. 5

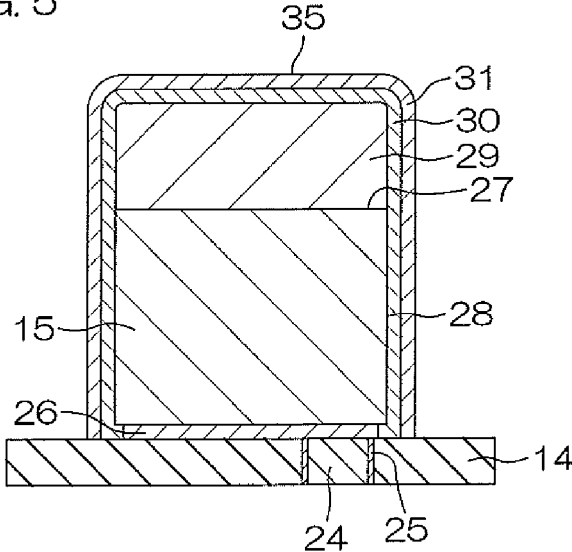


FIG. 6

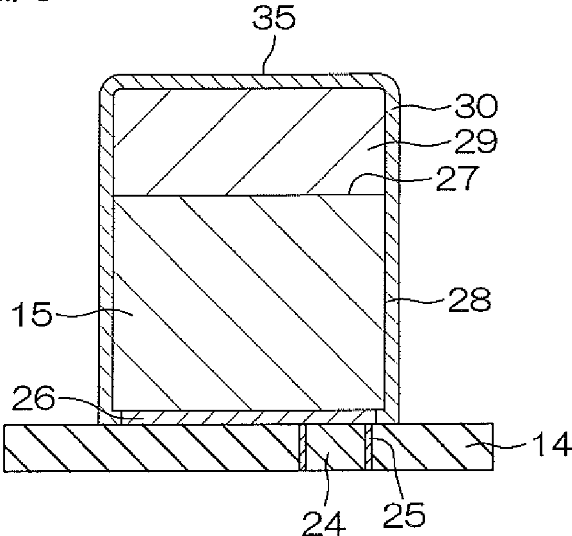


FIG. 7

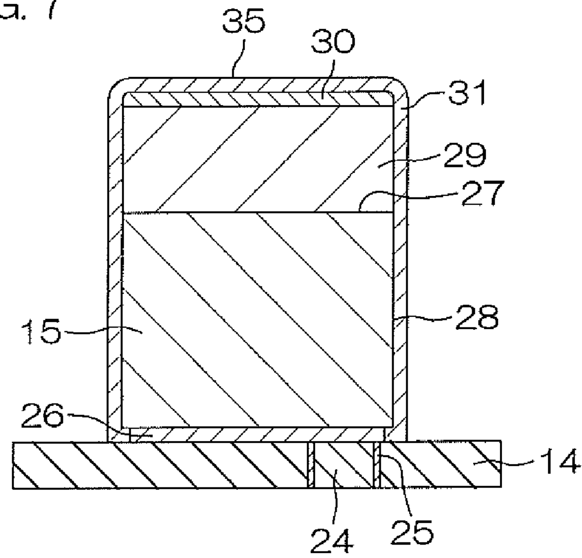


FIG. 8

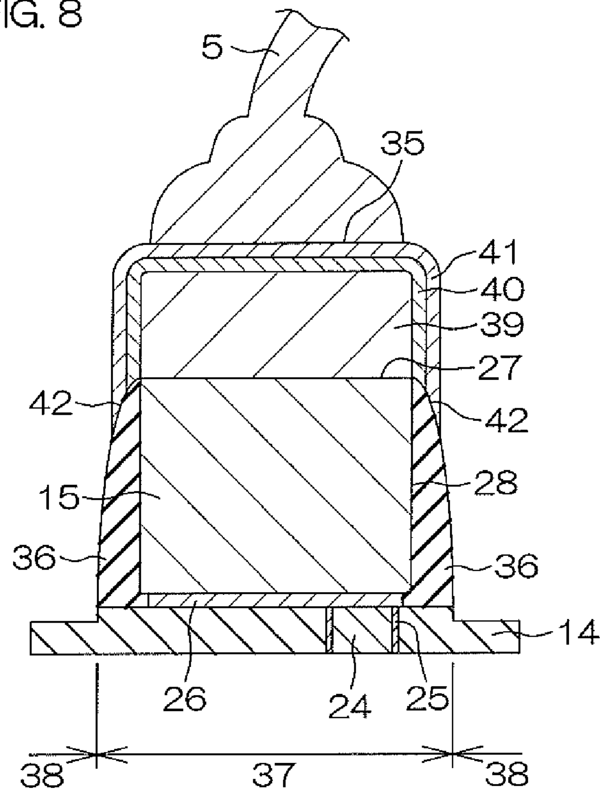


FIG. 9A

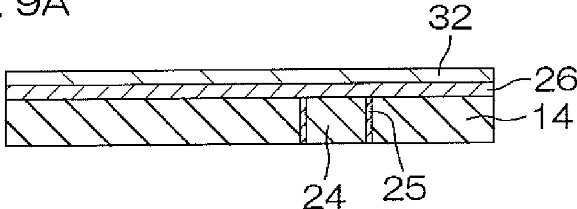


FIG. 9B

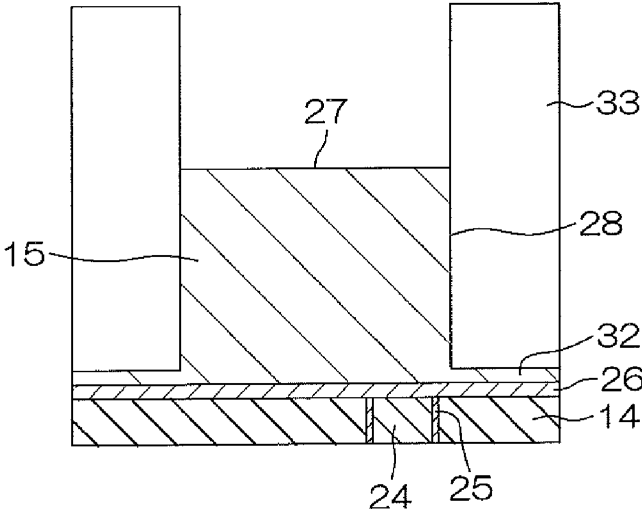
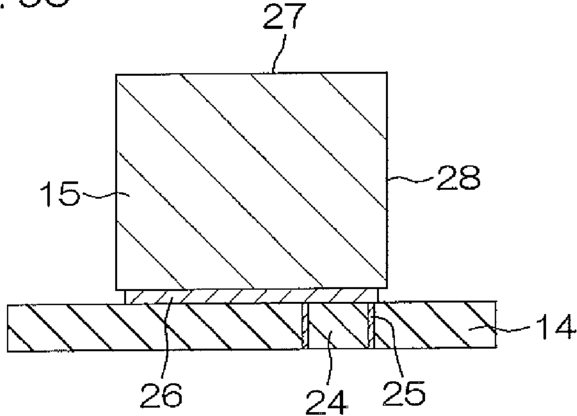


FIG. 9C



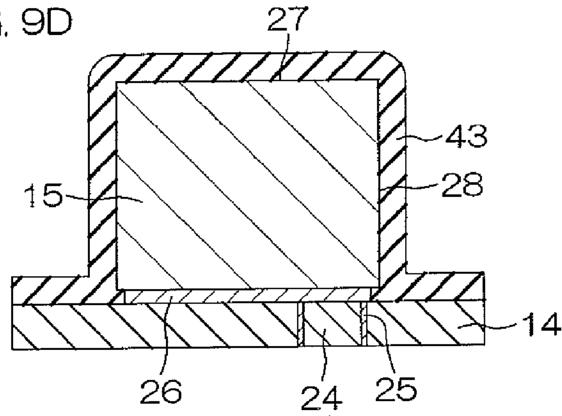


FIG. 9D
27
43
28
15
14
26
24
25

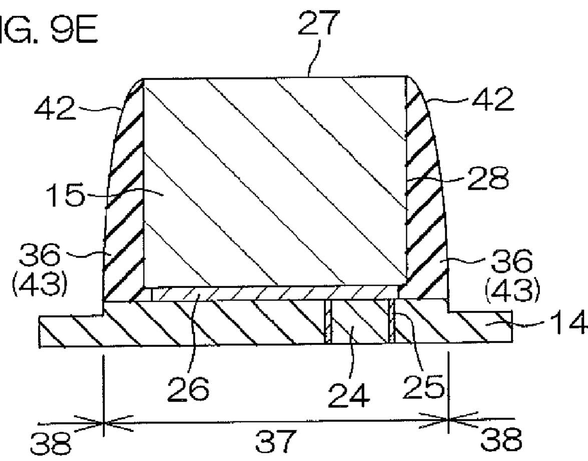


FIG. 9E
27
42
42
28
15
36
(43)
36
(43)
14
26
24
25
38
37
38

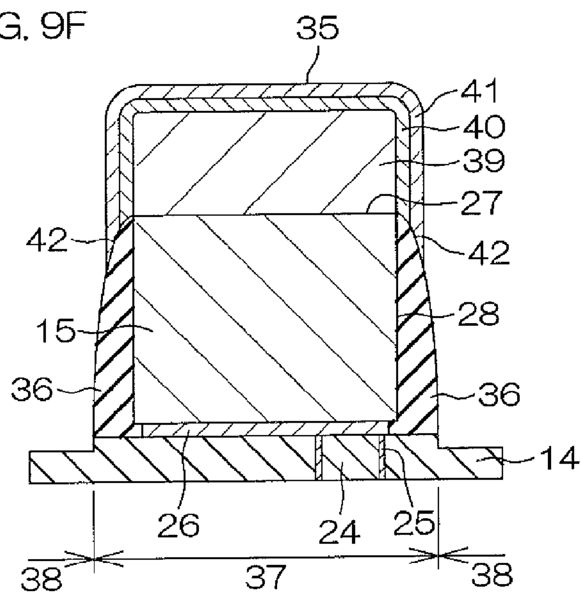


FIG. 9F
35
41
40
39
27
42
42
28
15
36
36
14
26
24
25
38
37
38

FIG. 10

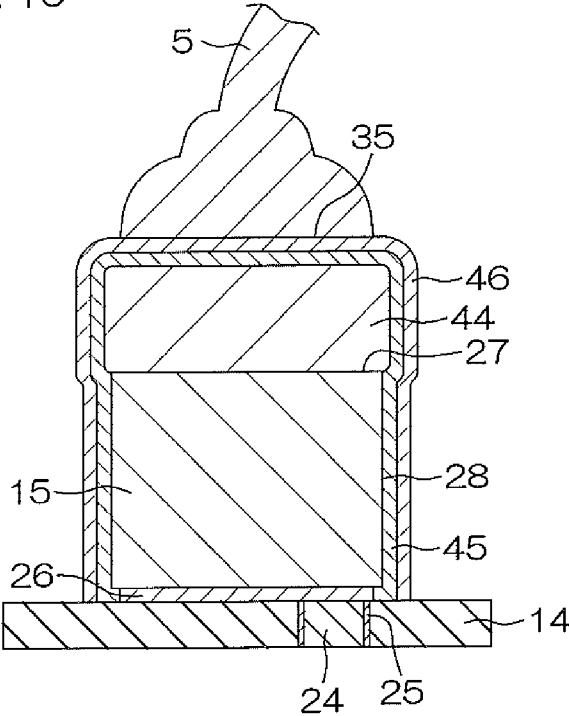


FIG. 11A

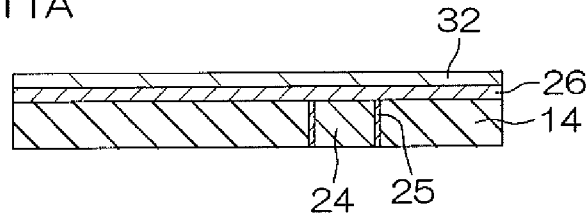


FIG. 11B

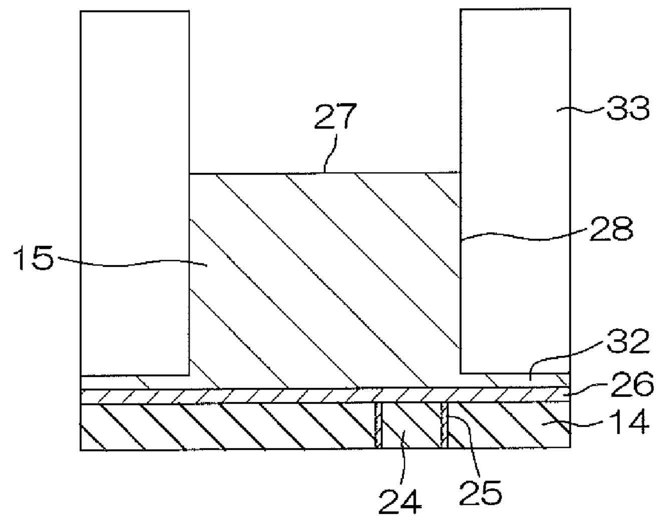
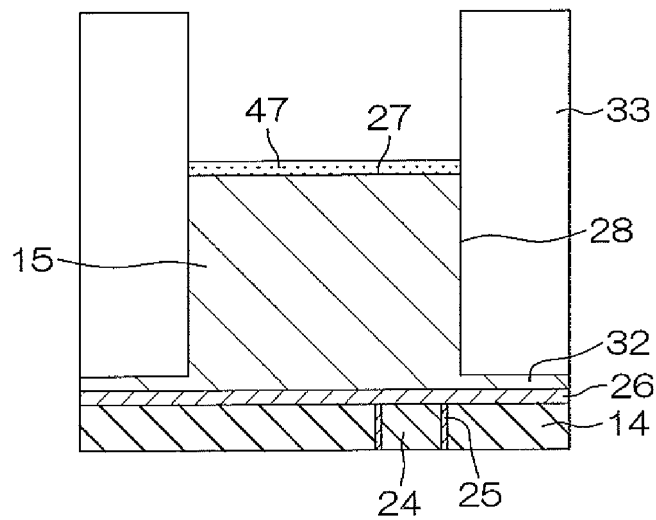


FIG. 11C



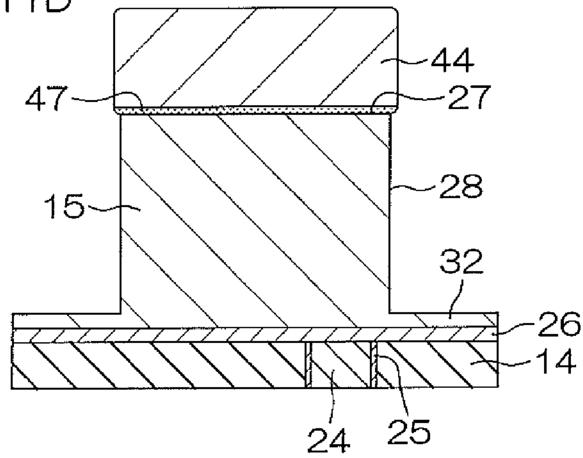


FIG. 11D
44
47
27
28
15
32
26
14
24
25

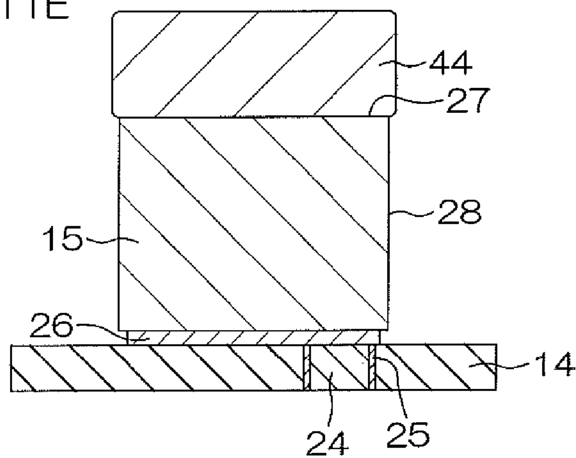


FIG. 11E
44
27
28
15
26
14
24
25

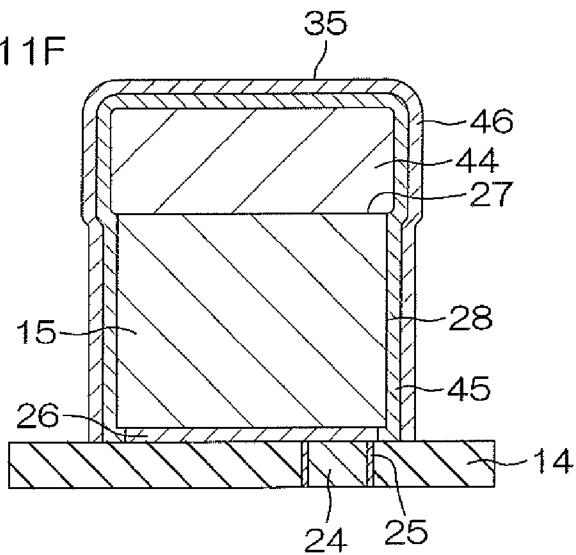


FIG. 11F
35
46
44
27
28
15
45
26
14
24
25

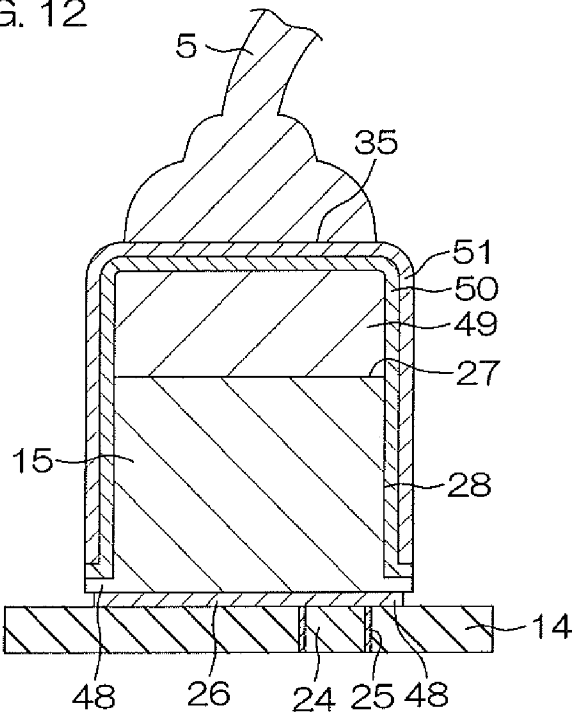


FIG. 12
5
35
51
50
49
27
15
28
14
48
26
24
25
48

FIG. 13A

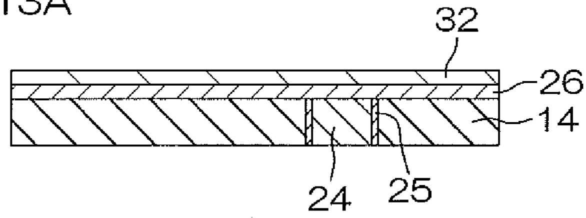


FIG. 13B

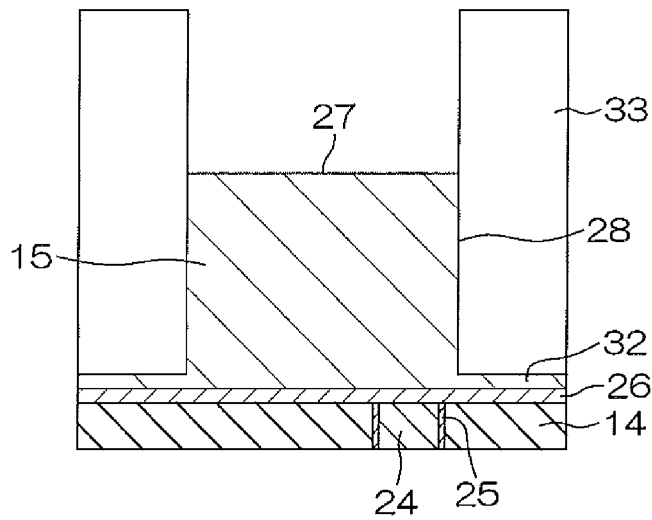


FIG. 13C

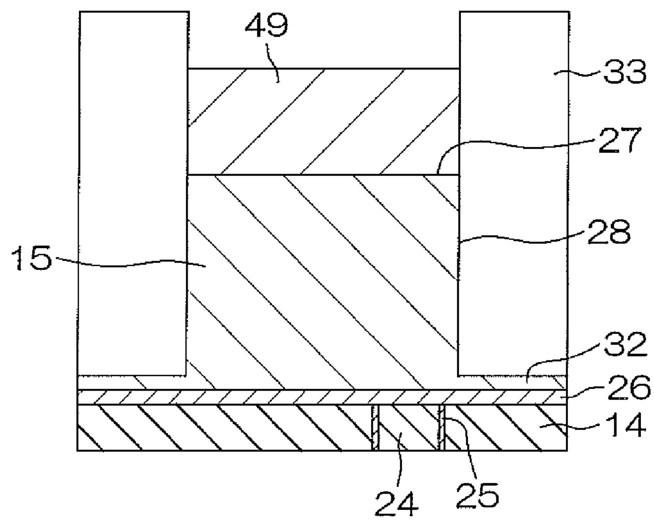


FIG. 13D

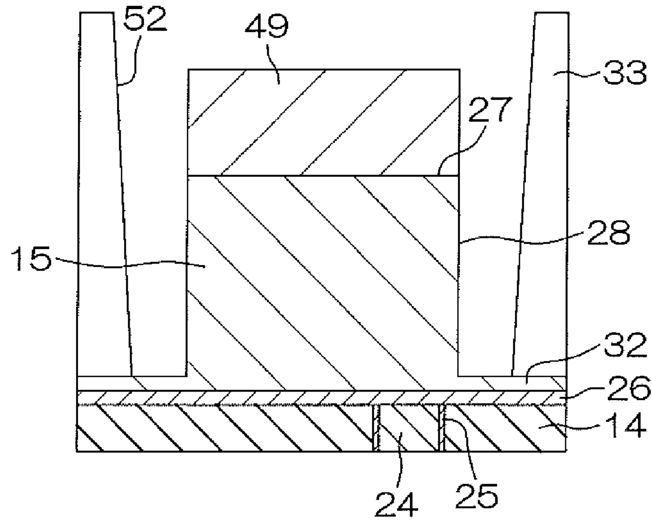
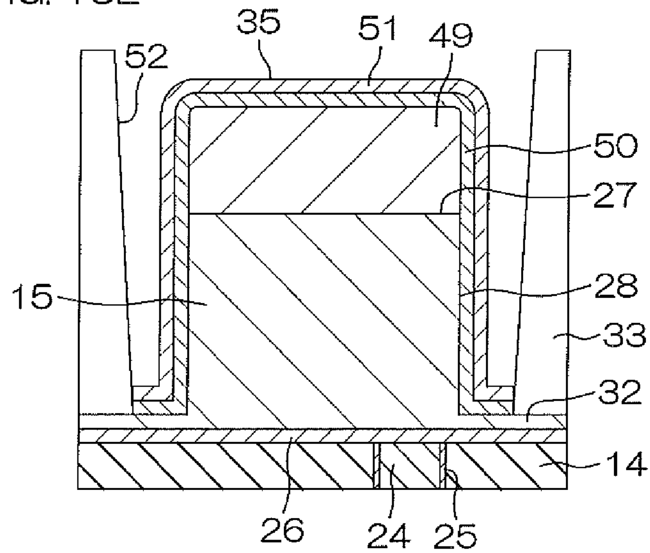


FIG. 13E



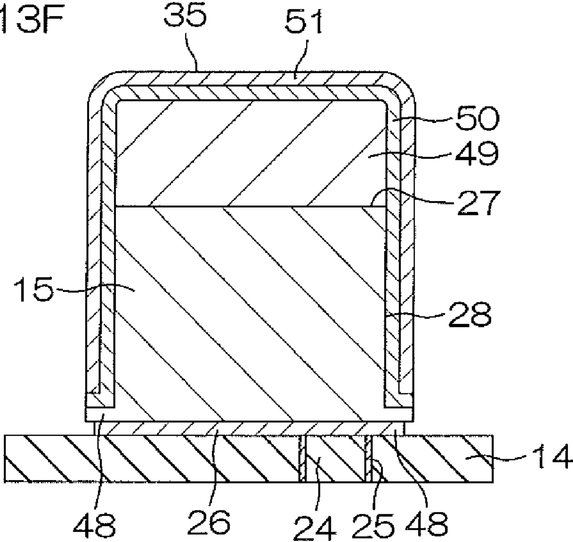


FIG. 13F
35
51
50
49
27
15
28
14
48
26
24
25
48

FIG. 14

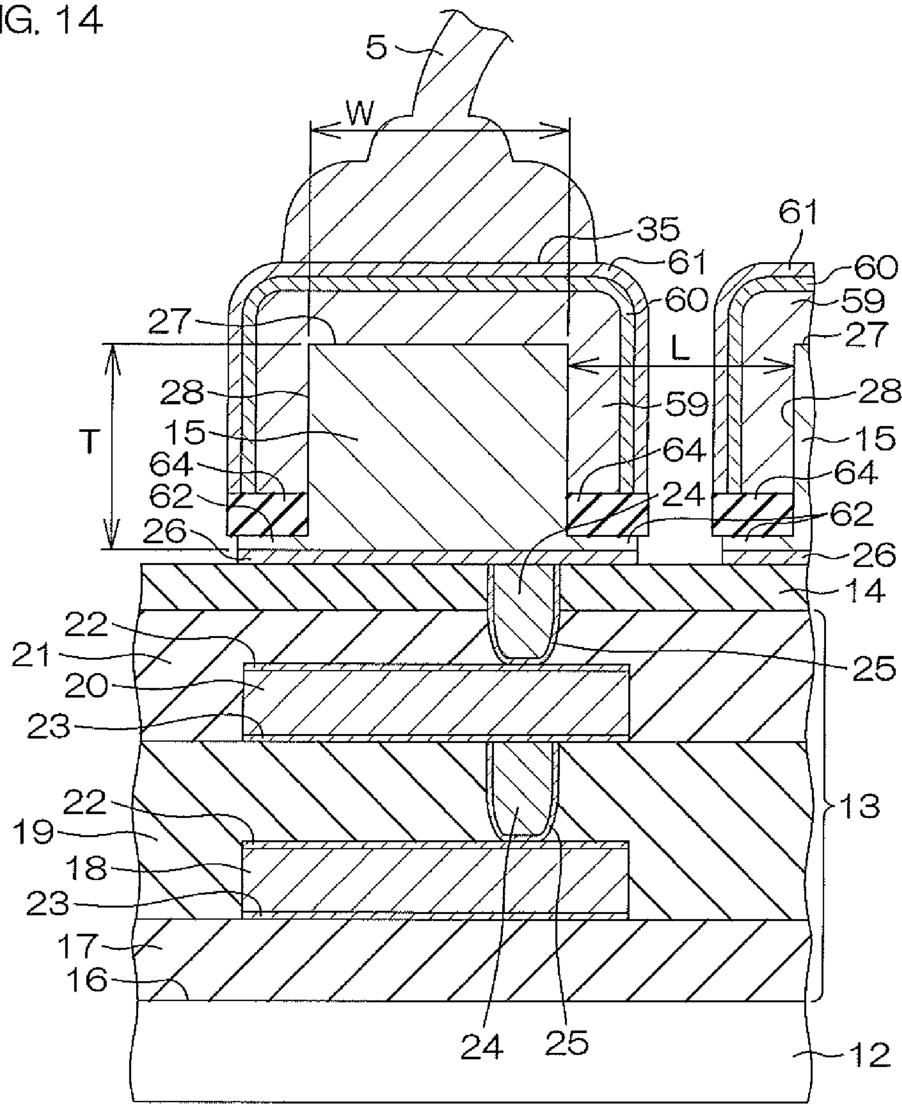


FIG. 15A

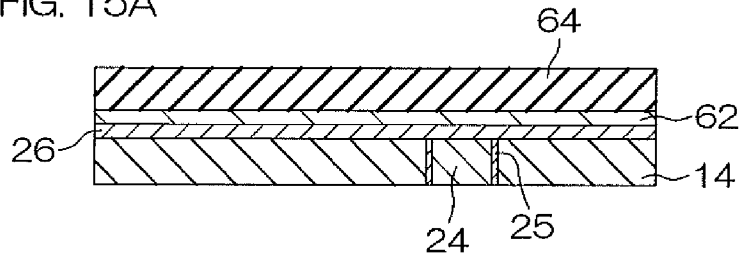


FIG. 15B

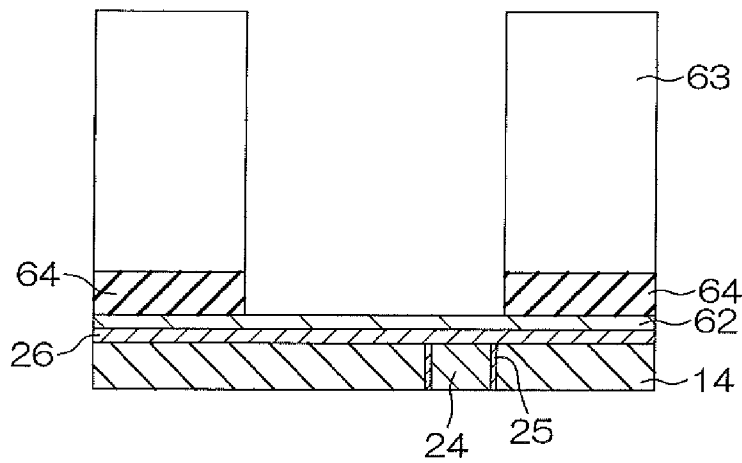
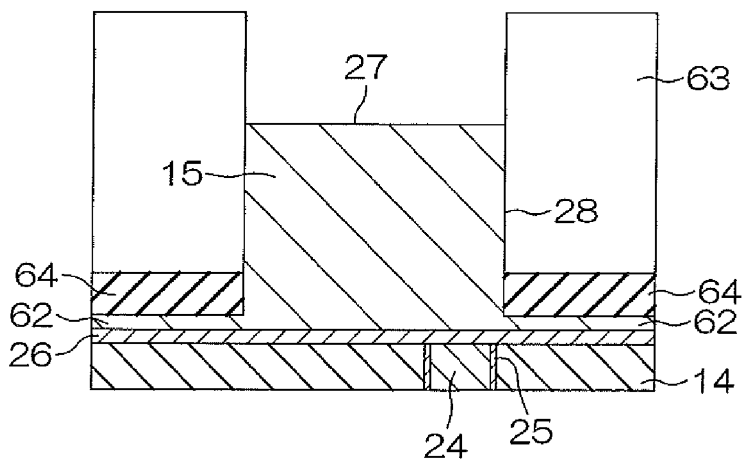


FIG. 15C



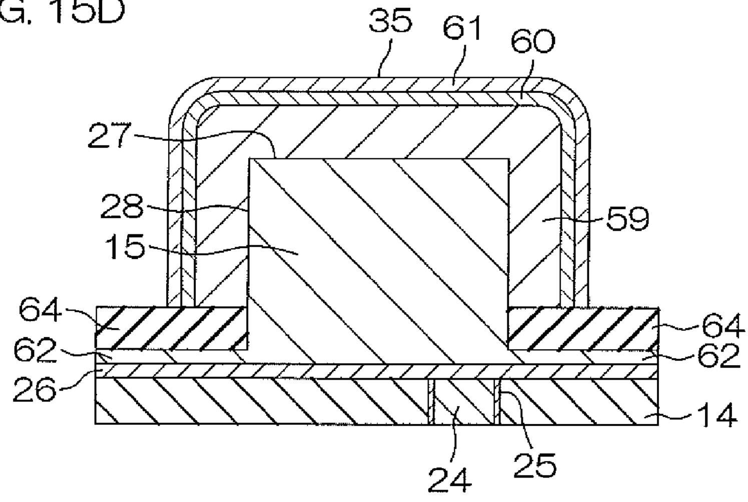


FIG. 15D
35
61
60
27
28
15
59
64
62
26
64
62
14
24
25

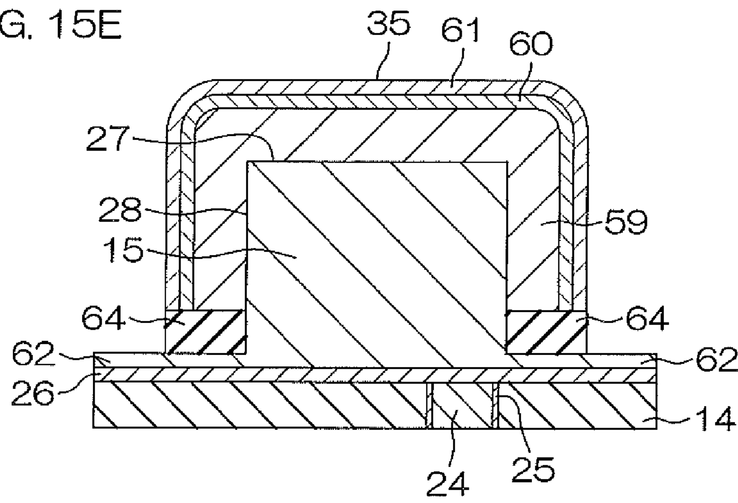


FIG. 15E
35
61
60
27
28
15
59
64
62
26
64
62
14
24
25

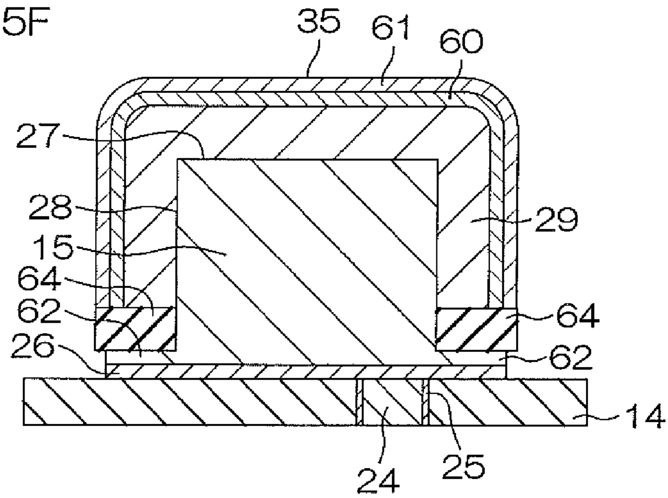


FIG. 15F
35
61
60
27
28
15
29
64
62
26
64
62
14
24
25

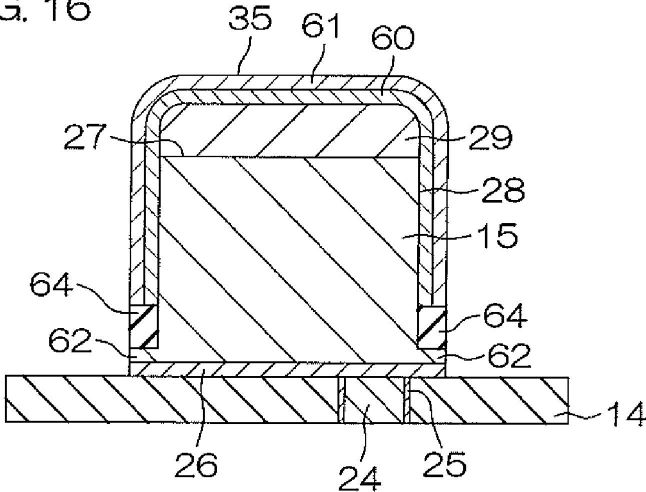


FIG. 16
35
61
60
27
29
28
15
64
64
62
62
14
26
24
25

SEMICONDUCTOR DEVICE

CROSS-REFERENCE TO RELATED APPLICATIONS

The present application corresponds to Japanese Patent Application No. 2013-78758 filed in the Japan Patent Office on Apr. 4, 2013 and Japanese Patent Application No. 2013-78759 filed in the Japan Patent Office on Apr. 4, 2013, and the entire disclosures of these applications are incorporated herein by reference.

FIELD OF THE INVENTION

The present invention relates to a semiconductor device that has copper wirings for wire connection.

BACKGROUND ART

It is heretofore known to use copper wirings in a layer to which a bonding wire is connected in order to achieve low resistance.

For example, Patent Literature 1 (Japanese Patent Application Publication No. 2001-319946) discloses a semiconductor device that includes a copper electrode formed on an dielectric substance, a barrier layer made of Ni or the like formed on the copper electrode, and an outermost layer made of Au or the like formed on the barrier layer, and a wire is connected to the outermost layer.

In a process for manufacturing this semiconductor device, both the barrier layer and the outermost layer covering the copper electrode are formed by first forming a seed metal on the surface of the copper electrode and then allowing each material to grow from this seed metal according to electroless plating.

BRIEF SUMMARY OF THE INVENTION

There is a need to form a comparatively thick Ni layer on the copper electrode in order to absorb shocks during wire bonding. However, if a method in which materials are grown isotropically from a seed film is employed in the same way as in electroless plating, Ni will develop plating growth also in a lateral direction of the copper electrode, and therefore an interval between Ni layers on adjacent copper electrodes is liable to be narrowed. Therefore, there is a fear that residues that have been plated along therewith when Ni develops plating growth will become a leak path, and a wire-to-wire short circuit will occur. To prevent this problem, the interval (wire-to-wire distance) between mutually adjacent copper electrodes is required to be widened, this making it difficult to greatly reduce wirings in size.

On the other hand, plating growth may be developed in a state in which the side surface of the copper electrode is covered with a resist film or the like, and, if so, a plated layer will not be formed on the side surface of the copper electrode, and the side surface of the copper electrode will be bared. In this case, there is a fear that the copper electrode will be oxidized from its side surface and will be corroded.

An object of the present invention is to provide a semiconductor device including copper wirings for wire connection that is capable of protecting a side surface of a copper wiring and that is capable of shortening a wiring-to-wiring distance.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. **1** is a schematic bottom view of a semiconductor device according to an embodiment of the present invention.

FIG. **2** is a cross-sectional view along cutting plane II-II of FIG. **1**.

FIG. **3** is an enlarged view of a part enclosed by a broken-line circle III of FIG. **2**, showing a first embodiment of a copper wiring.

FIG. **4**A to FIG. **4**F are views to describe a part of a process for manufacturing the copper wiring of FIG. **3**.

FIG. **5** is a view showing a modification of the copper wiring of FIG. **3**.

FIG. **6** is a view showing another modification of the copper wiring of FIG. **3**.

FIG. **7** is a view showing still another modification of the copper wiring of FIG. **3**.

FIG. **8** is a view showing a second embodiment of the copper wiring.

FIG. **9**A to FIG. **9**F are views to describe a part of a process for manufacturing the copper wiring of FIG. **8**.

FIG. **10** is a view showing a third embodiment of the copper wiring.

FIG. **11**A to FIG. **11**F are views to describe a part of a process for manufacturing the copper wiring of FIG. **10**.

FIG. **12** is a view showing a fourth embodiment of the copper wiring.

FIG. **13**A to FIG. **13**F are views to describe a part of a process for manufacturing the copper wiring of FIG. **12**.

FIG. **14** is a view showing a reference example of the copper wiring.

FIG. **15**A to FIG. **15**F are views to describe a part of a process for manufacturing the copper wiring of FIG. **14**.

FIG. **16** is a view showing a modification of the copper wiring of FIG. **14**.

DETAILED DESCRIPTION OF THE INVENTION

The semiconductor device of the present invention includes an insulating layer, a copper wiring for wire connection formed on the insulating layer, a shock absorbing layer formed on an upper surface of the copper wiring, the shock absorbing layer being made of a metallic material with a hardness higher than copper, a bonding layer formed on the shock absorbing layer, the bonding layer having a connection surface for a wire, and a side protecting layer covering a side surface of the copper wiring, wherein the side protecting layer has a thickness thinner than a distance from the upper surface of the copper wiring to the connection surface of the bonding layer.

According to this arrangement, the thickness of the side protecting layer is thinner than the distance from the upper surface of the copper wiring to the connection surface of the bonding layer. Therefore, when a plurality of copper wirings are disposed, the distance between the side protecting layers of adjacent copper wirings can be secured more widely than in a conventional example. As a result, the occurrence of a wiring-to-wiring short circuit can be prevented even if the wiring-to-wiring distance of the copper wiring is shortened.

Additionally, the copper wiring is covered with the shock absorbing layer, with the bonding layer, and with the side protecting layer, and its surface is not exposed, and therefore the copper wiring can be restrained from being oxidized or corroded.

The shock absorbing layer may be selectively formed only on the upper surface of the copper wiring.

According to this arrangement, the thickness of the layer on the side surface of the copper wiring can be made thinner

in proportion to an extent resulting from the fact that the shock absorbing layer is not formed on the side surface of the copper wiring.

The bonding layer may have a first portion covering the side surface of the copper wiring and a second portion covering an upper surface of the shock absorbing layer, and the side protecting layer may include the first portion of the bonding layer.

According to this arrangement, the side protecting layer can be formed simultaneously with the formation of the bonding layer, and therefore the manufacturing process can be simplified.

The side protecting layer may completely cover the side surface of the copper wiring from an upper end to a lower end of the copper wiring.

According to this arrangement, the copper wiring can be reliably prevented from being oxidized or corroded by completely covering the side surface of the copper wiring.

On the other hand, the copper wiring may have a projecting portion projecting outwardly at the lower end of the side surface thereof, and the side protecting layer may cover the side surface of the copper wiring from the upper end of the copper wiring to the projecting portion.

The side protecting layer may include a sidewall made of an insulating material.

According to this arrangement, the side protecting layer is made of an insulating material, and therefore the occurrence of a wiring-to-wiring short circuit can be prevented more excellently.

Preferably, the sidewall is made of an SiN film.

The shock absorbing layer may have a side surface flush with the side surface of the copper wiring.

According to this arrangement, the side surface of the shock absorbing layer and the side surface of the copper wiring are flush with each other, and therefore the bonding layer can be excellently formed near an interface therebetween.

On the other hand, the shock absorbing layer may project more sidewardly than the copper wiring such that a level difference is formed between a side surface of the shock absorbing layer and the side surface of the copper wiring.

The shock absorbing layer may have a first portion covering the side surface of the copper wiring and a second portion covering the upper surface of the copper wiring, the first portion may have a thickness thinner than a thickness of the second portion, and the side protecting layer may include the first portion of the shock absorbing layer.

According to this arrangement, the thickness of the layer formed on the side surface of the copper wiring can be made thinner in proportion to an extent resulting from the fact that the shock absorbing layer is thinned at the first portion. Additionally, the side protecting layer can be formed simultaneously with the formation of the shock absorbing layer, and therefore the manufacturing process can be simplified.

Preferably, the bonding layer may have a first portion covering the first portion of the shock absorbing layer and a second portion covering the second portion of the shock absorbing layer, and the side protecting layer further may include the first portion of the bonding layer.

The shock absorbing layer may be made of an Ni film. Additionally, the bonding layer may include a stacked structure consisting of a Pd film and an Au film stacked in this order from the shock absorbing layer. Additionally, in the semiconductor device of the present invention, a barrier film may be interposed between the insulating layer and the copper wiring.

The barrier film may have an end portion disposed more inside than the side surface of the copper wiring.

The side protecting layer may enter a level difference between the side surface of the copper wiring and the end portion of the barrier film below the copper wiring.

The barrier film may be made of Ti.

A plurality of copper wirings each of which is the copper wiring may be formed at a wiring-to-wiring distance of less than 20 μm.

According to this arrangement, the wiring-to-wiring distance is less than 20 μm, and therefore the wiring can be greatly reduced.

A part of the shock absorbing layer disposed on the upper surface of the copper wiring may be 2 μm to 4 μm thickness.

The semiconductor device of the present invention may further include a semiconductor substrate and a multilayer wiring structure disposed on the semiconductor substrate, and the insulating layer may include a passivation film formed on a topmost surface of the multilayer wiring structure.

Embodiments of the present invention and a reference example will be hereinafter described in detail with reference to the accompanying drawings.

FIG. **1** is a schematic bottom view of a semiconductor device **1** according to an embodiment of the present invention. FIG. **2** is a cross-sectional view along cutting plane II-II of FIG. **1**.

The semiconductor device **1** is a semiconductor device to which a QFN (Quad Flat Non-leaded Package) has been applied, and has a structure in which a semiconductor chip **2** is sealed with a resin package **6** along with a die pad **3**, a lead **4**, and a copper wire **5**. The external shape of the semiconductor device **1** (resin package **6**) is a flat rectangular parallelepiped shape.

The exterior of the semiconductor device **1** is, for example, planarly in a square shape of 4 mm square, and is, for example, a hexahedron of 0.85 mm in thickness, and the dimensions of each portion of the semiconductor device **1** mentioned below are one example in a case in which the semiconductor device **1** has those external dimensions.

The semiconductor chip **2** is in a square shape of 2.3 mm when viewed planarly. The thickness of the semiconductor chip **2** is 0.23 mm. A plurality of pads **7** are disposed at a peripheral edge of a surface of the semiconductor chip **2**. Each pad **7** is electrically connected to a semiconductor element built on a semiconductor substrate **12** described later. Aback metal **8** made of a metallic layer, such as Au, Ni (nickel), or Ag (silver), is formed on a back surface of the semiconductor chip **2**.

The die pad **3** and the lead **4** are formed by punching a thin metal plate (e.g., thin copper plate). The thickness of the thin metal plate (the die pad **3** and the lead **4**) is 0.2 mm. A plated layer **9** made of Ag is formed on the surface of the die pad **3** and on the surface of the lead **4**.

The die pad **3** is in a square shape of 2.7 mm when viewed planarly, and is disposed at the middle of the semiconductor device **1** such that each side surface of the die pad **3** becomes parallel to the side surface of the semiconductor device **1**.

A hollow having a substantially ¼ elliptical shape in the cross section is formed at a peripheral edge of the back surface of the die pad **3** over its entire periphery by performing a squeezing operation from the back surface side. The resin package **6** enters the hollow. As a result, the peripheral edge of the die pad **3** is brought into a sandwiched state by means of the resin package **6** from its upper and lower sides, and the die pad **3** is prevented from dropping off (from falling out) from the resin package **6**.

Additionally, the back surface of the die pad **3** is exposed from the back surface of the resin package **6** except its peripheral edge (except a hollowed part having a substantially ¼ elliptical shape in the cross section).

The lead **4** is disposed at positions that face each side surface of the die pad **3** so as to be the same in number (e.g., nine leads). At each position facing the side surface of the die pad **3**, the leads **4** extend in a direction perpendicular to the side surface faced thereby, and are evenly spaced in a direction parallel to this side surface. The length in the longitudinal direction of the lead **4** is 0.45 mm. The interval between the die pad **3** and the lead **4** is 0.2 mm.

A hollow having a substantially ¼ elliptical shape in the cross section is formed at a die-pad-side end of the back surface of the lead **4** by performing a squeezing operation from the back surface side. The resin package **6** enters the hollow. As a result, the die-pad-side end of the lead **4** is brought into a sandwiched state by means of the resin package **6** from its upper and lower sides, and the lead **4** is prevented from dropping off (from falling out) from the resin package **6**.

The back surface of the lead **4** is exposed from the back surface of the resin package **6** except the die-pad-side end (except a hollowed part having a substantially ¼ elliptical shape in the cross section). A side surface opposite to the die-pad side of the lead **4** is exposed from the side surface of the resin package **6**.

A plated layer **10** made of solder is formed on parts exposed from the resin package **6** of the back surface of the die pad **3** and of the back surface of the lead **4**.

The semiconductor chip **2** has its back surface bonded to the surface (plated layer **10**) of the die pad **3** with a junction material **11** therebetween in a state in which its surface on which the pad **7** is placed is directed upwardly. For example, a solder paste is used as the junction material **11**. The thickness of the junction material **11** is 0.02 mm.

If an electric connection between the semiconductor chip **2** and the die pad **3** is unnecessary, the back metal **8** may be excluded, and the back surface of the semiconductor chip **2** may be bonded to the surface of the die pad **3** with a junction material made of an insulating paste, such as a silver paste, therebetween. In this case, the planar size of the semiconductor chip **2** is 2.3 mm square. Additionally, the plated layer **9** on the surface of the die pad **3** may be excluded.

The copper wire **5** is made of, for example, copper whose purity is 99.99% or more. One end of the copper wire **5** is bonded to the pad **7** of the semiconductor chip **2**. The other end of the copper wire **5** is bonded to the surface of the lead **4**. The copper wire **5** is stretched between the semiconductor chip **2** and the lead **4** while drawing an arched loop. A difference in height between the top of the loop of the copper wire **5** and the surface of the semiconductor chip **2** is 0.16 mm.

Next, four embodiments of the pad **7** (copper wiring **15**) will be described along with a structure of the semiconductor chip **2**.

<First Embodiment>

FIG. **3** is an enlarged view of a part enclosed by a broken-line circle III of FIG. **2**, and shows a first embodiment of the copper wiring **15**.

The semiconductor chip **2** includes the semiconductor substrate **12**, a lower wiring **13**, a passivation film **14** that is one example of an insulating layer of the present invention, and the copper wiring **15**.

For example, the semiconductor substrate **12** is a silicon substrate having a surface **16** on which semiconductor elements (diodes, transistors, resistors, capacitors, etc.) are formed.

The lower wiring **13** has a multilayer wiring structure in which a plurality of wiring layers are stacked together with an interlayer film therebetween in order from the surface **16** of the semiconductor substrate **12**. In the present embodiment, the lower wiring **13** includes a first metal layer **18** stacked on the surface **16** of the semiconductor substrate **12** with a first interlayer film **17** therebetween, a second metal layer **20** stacked on the first metal layer **18** with a second interlayer film **19** therebetween, and a third interlayer film (uppermost interlayer film) **21** covering the second metal layer **20**.

The first interlayer film **17**, the second interlayer film **19**, and the third interlayer film **21** are made of an insulation material such as silicon oxide (SiO_2). The first metal layer **18** and the second metal layer **20** are made of aluminum (aluminum wiring). Let it be supposed that pure aluminum that contains 100% Al and an aluminum alloy consisting of Al and other metals (e.g., Al—Cu alloy, Al—Si alloy, Al—Si—Cu alloy, etc.) are included in "aluminum" used for the wiring of the present embodiment (the same applies hereinafter).

Barrier films **22** and **23** that prevent impurities from diffusing into the first to third interlayer films **17**, **19**, and **21** are formed on the upper and lower surfaces of the first metal layer **18** and on those of the second metal layer **20**, respectively. The upper barrier films **22** formed on the upper surfaces of the first and second metal layers **18** and **20** are made of, for example, titanium nitride (TiN). On the other hand, the lower barrier films **23** formed on the lower surfaces of the first and second metal layers **18** and **20** have, for example, a two-layer structure (TiN/Ti) in which titanium nitride (TiN) and titanium (Ti) are stacked together in this order from the lower surfaces of the first and second metal layers **18** and **20**.

The passivation film **14** is made of an insulating material such as silicon nitride (SiN). The passivation film **14** is formed on the third interlayer film **21**.

Vias **24** that penetrate the insulating films over the upper surfaces of the first and second metal layers **18** and **20** are connected to the upper surfaces of the first and second metal layers **18** and **20**, respectively. In the present embodiment, the via **24** connected to the upper surface of the first metal layer **18** penetrates the second interlayer film **19**, and is connected to the lower surface of the second metal layer **20**. On the other hand, the via **24** connected to the upper surface of the second metal layer **20** penetrates the third interlayer film **21** and the passivation film **14**, and is exposed from the surface of the passivation film **14** so as to become flush with this surface. This exposed part is connected to the lower surface of the copper wiring **15** as describe later. A barrier film **25** made of, for example, titanium nitride (TiN) is interposed between the via **24** and the insulating film (in the present embodiment, the second interlayer film **19**, the third interlayer film **21**, and the passivation film **14**).

The copper wiring **15** is made of, for example, copper (e.g., high-purity copper whose purity is 99.9999% (6N) or more or whose purity is 99.99% (4N) or more and, in some cases, including a slight amount of impurities), and a plurality of copper wirings **15** are spaced on the passivation film **14**. In the present embodiment, the distance (wiring-to-wiring distance L) between adjacent copper wirings **15** is, for example, less than 20 μm, and, preferably, about 10 μm. Each copper wiring **15** is formed in a quadrangle that has an

upper surface **27** and a side surface **28** when viewed cross-sectionally along the normal direction of the passivation film **14** (hereinafter, referred to simply as "when viewed cross-sectionally"). The size of the thus shaped copper wiring **15** is, for example, about 7 μm to 10 μm in thickness T, and is, for example, about 10 μm in width W.

Additionally, each copper wiring **15** is formed so as to cover the via **24** exposed from the surface of the passivation film **14**, and is connected to the via **24** through the barrier film **26** interposed between the passivation film **14** and the copper wiring **15**.

In the present embodiment, the barrier film **26** is made of, for example, titanium (Ti). Additionally, the barrier film **26** is formed such that its both ends are located inside the side surface **28** of the copper wiring **15** when viewed cross-sectionally.

An Ni (nickel) film **29** that is one example of a shock absorbing layer of the present invention, a Pd (palladium) film **30** that is one example of a bonding layer of the present invention, and an Au (gold) film **31** are stacked together in this order from the copper wiring **15** in such a way as to cover each copper wiring **15**.

The Ni film **29** is formed such that its one surface and its other surface follow the upper surface **27** and the side surface **28** of the copper wiring **15**, and covers the upper surface **27** and the side surface **28**. Additionally, the Ni film **29** enters a level difference (groove) formed between the side surface **28** and the end of the barrier film **26** below the side surface **28**. In the Ni film **29**, a part contiguous to the side surface **28** of the copper wiring **15** is selectively thinner than a part contiguous to the upper surface **27**. In the Ni film **29**, the thickness of the part contiguous to the upper surface **27** is, for example, 2 μm to 4 μm, whereas the thickness of the part contiguous to the side surface **28** is thinner than the foregoing one, and is, for example, 0 μm to 1 μm.

The Pd film **30** is formed such that its one surface and its other surface follow the upper surface **27** and the side surface **28** of the copper wiring **15**, and covers the upper surface and the side surface of the Ni film **29**. The Pd film **30** is formed with a uniform thickness. The thickness of the Pd film **30** is, for example, 0.1 μm to 0.5 μm.

The Au film **31** is formed such that its one surface and its other surface follow the upper surface **27** and the side surface **28** of the copper wiring **15**, and covers the upper surface and the side surface of the Pd film **30**. The Au film **31** is formed with a uniform thickness that is thinner than the Pd film **30**. The thickness of the Au film **31** is, for example, 0 μm to 0.05 μm.

These stacked films **29** to **31** consisting of the Ni film **29**, the Pd film **30**, and the Au film **31** protect the side surface **28** of the copper wiring **15** by covering the side surface **28** as one example of a side protecting layer of the present invention. Additionally, a difference in the film thickness is provided to the Ni film **29** in these stacked films **29** to **31**, and therefore a part on the side surface **28** of the copper wiring **15** is thinner than the distance from the upper surface **27** of the copper wiring **15** to a wire connection surface **35** (upper surface of the Au film **31**) of the copper wire **5** in the stacked films **29** to **31**.

In the present embodiment, the copper wiring **15** coated with the Ni film **29**, with the Pd film **30**, and with the Au film **31** is exposed to the surface of the semiconductor chip **2** in the form of the pad **7**. The copper wire **5** is bonded to the Au film **31** exposed to the topmost surface of the pad **7**.

Next, a process for manufacturing the copper wiring **15** of the first embodiment will be described.

FIG. **4**A to FIG. **4**F are views to describe a part of the manufacturing process of the copper wiring **15** of FIG. **3** in order of process steps. In the following description, let it be supposed that electrolytic plating is performed in a temperature environment of, for example, room temperature (about 20° C. or 25° C.) and that electroless plating is performed in a plating solution of, for example, about 90° C.

First, before forming the copper wiring **15**, the lower wiring **13** (see FIG. **3**) is formed on the semiconductor substrate **12** (see FIG. **3**) according to a well-known multilayer wiring manufacturing technique, and then the passivation film **14** is formed, and the via **24** that penetrates this passivation film **14** is formed.

Thereafter, as shown in FIG. **4**A, the barrier film **26** and a copper seed film **32** are formed on the surface of the passivation film **14** in this order, for example, according to a sputtering method.

Thereafter, as shown in FIG. **4**B, a resist film **33** that is one example of a mask of the present invention selectively having an opening in a region in which each copper wiring **15** is to be formed is formed on the copper seed film **32**. Thereafter, copper is subjected to plating growth by means of electrolytic plating from the surface of the copper seed film **32** selectively exposed from the opening. As a result, the copper wiring **15** is formed. In this state, the copper wiring **15** has its side surface **28** covered with the resist film **33**. Additionally, adjacent copper wirings **15** are in a mutually electrically connected state through the copper seed film **32** covered with the resist film **33**.

Thereafter, as shown in FIG. **4**C, Ni is subjected to plating growth by means of electrolytic plating from the upper surface **27** of the copper wiring **15** selectively exposed from the opening of the resist film **33**. As a result, an upper-surface Ni film **34** (e.g., about 3 μm in thickness) brought into a sandwiched state from both sides by means of the resist film **33** is formed on the upper surface **27** of the copper wiring **15**.

Thereafter, as shown in FIG. **4**D, the resist film **33** is removed. As a result, the side surface **28** of the copper wiring **15** covered with the resist film **33** and the side surface of the upper-surface Ni film **34** covered with the resist film **33** are exposed.

Thereafter, as shown in FIG. **4**E, the copper seed film **32** other than the copper wiring **15** and the barrier film **26** disposed thereunder are selectively removed, for example, according to wet etching. At this time, the end of the barrier film **26** is etched more inwardly than the side surface **28** of the copper wiring **15** because of characteristics of wet etching (isotropic etching), and a level difference is created between the end of the barrier film **26** and the side surface **28**.

Thereafter, as shown in FIG. **4**F, Ni is subjected to plating growth by means of electroless plating from the entire surface (side surface **28**) of the exposed copper wiring **15** and from the entire surface of the upper-surface Ni film **34**. Although Ni isotropically develops plating growth with a uniform thickness because of electroless plating, the upper-surface Ni film **34** has already been formed on the upper surface **27** of the copper wiring **15**, and therefore, in the Ni film **29** formed after the growth, a part contiguous to the side surface **28** of the copper wiring **15** selectively becomes thinner than a part contiguous to the upper surface **27**. Thereafter, electroless plating is further performed, and Pd and Au are subjected to plating growth, and, as a result, the Pd film **30** and the Au film **31** are formed.

The copper wiring **15** coated with the stacked films **29** to **31** consisting of the Ni film **29**, the Pd film **30**, and the Au film **31** is formed through the steps mentioned above.

As described above, according to the present embodiment, the upper-surface Ni film **34** is formed before forming the stacked films **29** to **31** consisting of the Ni film **29**, the Pd film **30**, and the Au film **31** (see FIG. **4**C). As a result, a film thickness necessary to absorb shocks when the copper wire **5** is bonded can be secured in the region over the upper surface **27** of the copper wiring **15**. Therefore, when the stacked films **29** to **31** are subjected to electroless plating, it is only necessary to allow Ni to grow on the upper surface **27** of the copper wiring **15** so as to be comparatively thin, and therefore it is possible to thin the film thickness of Ni that simultaneously develops plating growth from the side surface **28** when Ni is subjected to plating growth. As a result, the stacked films **29** to **31** covering the side surface **28** of the copper wiring **15** can be made thinner than in a case in which Ni, Pd, and Au are evenly grown by electroless plating from the upper surface **27** and the side surface **28** of the bare copper wiring **15**.

As a result, the distance between the stacked films **29** to **31** of adjacent copper wirings **15** can be secured comparatively widely, and therefore the occurrence of a wiring-to-wiring short circuit can be prevented even if the wiring-to-wiring distance L of the copper wiring **15** is shortened. Additionally, the copper wiring **15** is completely covered with the stacked films **29** to **31** consisting of the Ni film **29**, the Pd film **30**, and the Au film **31**, and its surface is not exposed, and therefore the copper wiring **15** can be restrained from being oxidized or corroded.

Additionally, all platings can be treated by electroless plating after forming the upper-surface Ni film **34**. Electroless plating is bathtub type plating unlike one-by-one type electrolytic plating, and wafers can be treated at a time even if the wafers differ from each other in size. Therefore, the productivity of the semiconductor device **1** can be improved. Additionally, this electroless plating is performed after removing the resist film **33**, and therefore it is also possible to avoid the fact that the resist film **33** is deformed by being influenced by the plating temperature (about 90° C.) of electroless plating.

In the present embodiment, it is also possible to apply modifications shown in FIG. **5** to FIG. **7** to the copper wiring **15**.

For example, in FIG. **5**, the Ni film **29** is selectively formed only on the upper surface **27** so as to expose the side surface **28** of the copper wiring **15**. In this case, the side surface **28** of the copper wiring **15** is covered with the stacked films **30** and **31** consisting of the Pd film **30** and the Au film **31**. This arrangement can be obtained, for example, by forming the upper-surface Ni film **34** formed in FIG. **4**C as the Ni film **29** and by excluding the electroless plating of Ni in the step of FIG. **4**F. In other words, the Ni film **29** is formed by plating growth at the opening of the resist film **33**, and therefore its side surface is formed so as to be flush with the side surface **28** of the copper wiring **15** (so as to have no level difference).

Additionally, in FIG. **6**, the Au film **31** is also excluded in the arrangement of FIG. **5**. This arrangement can be obtained, for example, by further excluding the electroless plating of Au in the step of FIG. **4**F.

Additionally, in FIG. **7**, the Pd film **30** is also selectively formed only on the Ni film **29** in the arrangement of FIG. **5** so as to expose the side surface **28** of the copper wiring **15** in the same way as the Ni film **29**. In this case, the side surface **28** of the copper wiring **15** is covered with the single layer film of the Au film **31**. This arrangement can be obtained, for example, by forming the Pd film **30** by means of electrolytic plating after forming the Ni film **29** in the step of FIG. **4**C and by excluding the electroless plating of Pd in the step of FIG. **4**F. As a result, the Pd film **30** is also formed such that its side surface becomes flush with the side surface **28** of the copper wiring **15** (no level difference is created) in the same way as the Ni film **29** of FIG. **5**.

The stacked films or the single layer film covering the side surface **28** of the copper wiring **15** can be made thinner by these modifications than in conventional examples, and therefore it is possible to shorten the wiring-to-wiring distance L of the copper wiring **15** while preventing the occurrence of a wiring-to-wiring short circuit.

<Second Embodiment>

FIG. **8** is a view showing a second embodiment of the copper wiring **15**. In FIG. **8**, only the copper wiring **15** and regions therearound are shown, and the structure etc., of the semiconductor chip **2** are neither shown nor described. Additionally, in FIG. **8**, the same reference sign is given to a component equivalent to each component of FIG. **3** shown above, and a description of this component is omitted.

In this second embodiment, a sidewall **36** that is one example of the side protecting layer of the present invention is formed on the side surface **28** of each copper wiring **15**. As a result, the side surface **28** of the copper wiring **15** is protected by the sidewall **36**. The sidewall **36** is made of an insulating film selectively formed on the side surface **28** so as to expose the upper surface **27** of the copper wiring **15**. In the present embodiment, the sidewall **36** is made of an SiN film that is the same material as the passivation film **14**, and its thickness is, for example, 0.1 μm to 1 μm. Additionally, as shown in FIG. **8**, the sidewall **36** may have a tapered outer surface **42** inclined with respect to the side surface **28** by becoming thinner in proportion to an approach to the upper surface **27** from the lower surface of the copper wiring **15**.

Additionally, in the passivation film **14**, a non-wiring region **38** other than the formation region (wiring region **37**) of the copper wiring **15** coated with the sidewall **36** is formed in a concave portion by being selectively dug down, and, as a result, the wiring region **37** becomes a mesa portion that protrudes more outwardly than the non-wiring region **38**. In the present embodiment, the concave portion of the non-wiring region **38** is formed in a self-aligned manner with respect to the sidewall **36**.

An Ni (nickel) film **39** that is one example of the shock absorbing layer of the present invention, a Pd (palladium) film **40** that is one example of the bonding layer of the present invention, and an Au (gold) film **41** are stacked together in this order from the copper wiring **15** in such a way as to cover the upper surface **27** of the copper wiring **15** exposed from the sidewall **36**.

The Ni film **39** is formed with a uniform thickness on the upper surface **27** of the copper wiring **15** such that its side surface becomes flush with the side surface **28** of the copper wiring **15**. The thickness of the Ni film **39** is, for example, 2 μm to 4 μm.

The Pd film **40** is formed such that its one surface and its other surface follow the upper surface and the side surface of the Ni film **39**, and covers the upper surface and the side surface of the Ni film **39**, and covers the outer surface **42** of the sidewall **36** while crossing an interface between the Ni film **39** and the copper wiring **15**. The Pd film **40** is formed with a uniform thickness. The thickness of the Pd film **40** is, for example, 0.1 μm to 0.5 μm.

The Au film **41** is formed such that its one surface and its other surface follow the upper surface and the side surface of the Ni film **39**, and covers the upper surface and the side surface of the Pd film **40**, and covers the outer surface **42** of the sidewall **36** beside the Pd film **40** while crossing the interface between the Ni film **39** and the copper wiring **15**. The Au film **41** is formed with a uniform thickness that is thinner than the Pd film **40**. The thickness of the Au film **41** is, for example, 0 μm to 0.05 μm.

Additionally, in the present embodiment, the sidewall **36** is thinner than the layer thickness of the stacked films **39** to **41** consisting of the Ni film **39**, the Pd film **40**, and the Au film **41** (the distance from the upper surface **27** of the copper wiring **15** to the wire connection surface **35** of the stacked films **39** to **41**). The copper wiring **15** coated with the stacked films **39** to **41** consisting of the Ni film **39**, the Pd film **40**, and the Au film **41** and coated with the sidewall **36** is exposed to the surface of the semiconductor chip **2** in the form of the pad **7**. The copper wire **5** is bonded to the Au film **41** exposed to the topmost surface of the pad **7**.

Next, a process for manufacturing the copper wiring **15** of the second embodiment will be described.

FIG. **9**A to FIG. **9**F are views to describe a part of the manufacturing process of the copper wiring **15** of FIG. **8** in order of process steps. In the following description, let it be supposed that electrolytic plating is performed in a temperature environment of, for example, room temperature (about 20° C. or 25° C.) and that electroless plating is performed in a plating solution of, for example, about 90° C.

First, before forming the copper wiring **15**, the lower wiring **13** (see FIG. **3**) is formed on the semiconductor substrate **12** (see FIG. **3**) according to a well-known multilayer wiring manufacturing technique, and then the passivation film **14** is formed, and the via **24** that penetrates this passivation film **14** is formed.

Thereafter, as shown in FIG. **9**A, the barrier film **26** and the copper seed film **32** are formed on the surface of the passivation film **14** in this order, for example, according to the sputtering method.

Thereafter, as shown in FIG. **9**B, the resist film **33** selectively having an opening in a region in which each copper wiring **15** is to be formed is formed on the copper seed film **32**. Thereafter, copper is subjected to plating growth by means of electrolytic plating from the surface of the copper seed film **32** selectively exposed from the opening. As a result, the copper wiring **15** is formed. In this state, the copper wiring **15** has its side surface **28** covered with the resist film **33**. Additionally, adjacent copper wirings **15** are in a mutually electrically connected state through the copper seed film **32** covered with the resist film **33**.

Thereafter, as shown in FIG. **9**C, the resist film **33** is removed. As a result, the side surface **28** of the copper wiring **15** covered with the resist film **33** is exposed. Thereafter, the copper seed film **32** other than the copper wiring **15** and the barrier film **26** disposed thereunder are selectively removed, for example, according to wet etching. At this time, the end of the barrier film **26** is etched more inwardly than the side surface **28** of the copper wiring **15** because of characteristics of wet etching (isotropic etching), and a level difference is created between the end of the barrier film **26** and the side surface **28**.

Thereafter, as shown in FIG. **9**D, an insulating film **43** is formed on the passivation film **14** so as to cover the copper wiring **15**, for example, according to a CVD method. This insulating film **43** is made of the same material as the sidewall **36**.

Thereafter, as shown in FIG. **9**E, the insulating film **43** is selectively removed, for example, according to etchback, and, as a result, the sidewall **36** is formed. In this case, a part of the surface of the passivation film **14** made of the same material as the insulating film **43** is subjected to over-etching, and, as a result, a concave portion of the non-wiring region **38** is formed.

Thereafter, as shown in FIG. **9**F, Ni, Pd, and Au are subjected to plating growth from the upper surface **27** of the copper wiring **15** exposed from the sidewall **36** by means of electroless plating. As a result, the Ni film **39**, the Pd film **40**, and the Au film **41** are formed.

The copper wiring **15** coated with the stacked films **39** to **41** consisting of the Ni film **39**, the Pd film **40**, and the Au film **41** and coated with the sidewall **36** is formed through the steps mentioned above.

As described above, according to the present embodiment, the sidewall **36** is formed before forming the stacked films **39** to **41** consisting of the Ni film **39**, the Pd film **40**, and the Au film **41**. Therefore, when the stacked films **39** to **41** are subjected to electroless plating, the materials of the stacked films **39** to **41** can be prevented from developing plating growth from the side surface **28** of the copper wiring **15**. Moreover, this sidewall **36** is thinner than the layer thickness of the stacked films **39** to **41**. As a result, the protection film (sidewall **36**) covering the side surface **28** of the copper wiring **15** can be made thinner than in a case in which Ni, Pd, and Au are evenly grown by electroless plating from the upper surface **27** and the side surface **28** of the bare copper wiring **15**.

As a result, the distance between the sidewalls **36** of adjacent copper wirings **15** can be secured comparatively widely, and therefore the occurrence of a wiring-to-wiring short circuit can be prevented even if the wiring-to-wiring distance L of the copper wiring **15** is shortened. Additionally, etching residues of the barrier film **26** generated in, for example, the step of FIG. **9**C can be removed together by applying over-etching onto a part of the surface of the passivation film **14** when the sidewall **36** is formed. As a result, Ni etc., can be prevented from developing plating growth at apart other than the copper wiring **15**, and therefore a wiring-to-wiring short circuit can be effectively prevented.

Additionally, the copper wiring **15** is completely covered with the stacked films **39** to **41** consisting of the Ni film **39**, the Pd film **40**, and the Au film **41** and covered with the sidewall **36**, and its surface is not exposed, and therefore the copper wiring **15** can be restrained from being oxidized or corroded.

Additionally, the platings of the Ni film **39**, the Pd film **40**, and the Au film **41** can be treated by electroless plating. Electroless plating is bathtub type plating unlike one-by-one type electrolytic plating, and wafers can be treated at a time even if the wafers differ from each other in size. Therefore, the productivity of the semiconductor device **1** can be improved. Additionally, this electroless plating is performed after removing the resist film **33**, and therefore it is also possible to avoid the fact that the resist film **33** is deformed by being influenced by the plating temperature (about 90° C.) of electroless plating.

In the second embodiment, an example in which the Au film **41** is excluded can be applied in the same way as in the modification of FIG. **6** of the first embodiment.

<Third Embodiment>

FIG. **10** is a view showing a third embodiment of the copper wiring **15**. In FIG. **10**, only the copper wiring **15** and regions therearound are shown, and the structure etc., of the

semiconductor chip **2** are neither shown nor described. Additionally, in FIG. **10**, the same reference sign is given to a component equivalent to each component of FIG. **3** shown above, and a description of this component is omitted.

In this third embodiment, an Ni (nickel) film **44** that is one example of the shock absorbing layer of the present invention, a Pd (palladium) film **45** that is one example of the bonding layer of the present invention, and an Au (gold) film **46** are stacked together in this order from the copper wiring **15** in such a way as to cover each copper wiring **15**.

The Ni film **44** projects more sidewardly than the copper wiring **15** when viewed cross-sectionally so as to create a level difference between its side surface and the side surface **28** of the copper wiring **15**, and is formed with a uniform thickness on the upper surface **27** of the copper wiring **15**. In other words, the Ni film **44** is selectively formed only at the upper surface **27** so as to expose the side surface **28** of the copper wiring **15**. A Pd catalyst (not shown) may be interposed between the Ni film **44** and the upper surface **27** of the copper wiring **15**. The thickness of the Ni film **44** is, for example, 2 μm to 4 μm.

The Pd film **45** is formed such that its one surface and its other surface follow the surface of the copper wiring **15** and the surface of the Ni film **44**, and covers the upper surface and the side surface of the Ni film **44** and covers the side surface **28** of the copper wiring **15** exposed from the Ni film **44**. The Pd film **45** is formed with a uniform thickness. The thickness of the Pd film **45** is, for example, 0.1 μm to 0.5 μm.

The Au film **46** is formed such that its one surface and its other surface follow the surface of the copper wiring **15** and the surface of the Ni film **44**, and covers the upper surface and the side surface of the Pd film **45**. The Au film **46** is formed with a uniform thickness that is thinner than the Pd film **45**. The thickness of the Au film **46** is, for example, 0 μm to 0.05 μm.

These stacked films **45** and **46** consisting of the Pd film **45** and the Au film **46** protect the side surface **28** of the copper wiring **15** by covering the side surface **28** as one example of the side protecting layer of the present invention. Additionally, the Ni film **44** is not formed at the side surface **28** in these stacked films **45** and **46**, and therefore a part on the side surface **28** of the copper wiring **15** is thinner than the distance from the upper surface **27** of the copper wiring **15** to the wire connection surface **35** (upper surface of the Au film **46**) of the copper wire **5** in the stacked films **45** and **46**.

In the present embodiment, the copper wiring **15** coated with the Ni film **44**, with the Pd film **45**, and with the Au film **46** is exposed to the surface of the semiconductor chip **2** in the form of the pad **7**. The copper wire **5** is bonded to the Au film **46** exposed to the topmost surface of the pad **7**.

Next, a process for manufacturing the copper wiring **15** of the third embodiment will be described.

FIG. **11**A to FIG. **11**F are views to describe a part of the manufacturing process of the copper wiring **15** of FIG. **10** in order of process steps. In the following description, let it be supposed that electrolytic plating is performed in a temperature environment of, for example, room temperature (about 20° C. or 25° C.) and that electroless plating is performed in a plating solution of, for example, about 90° C.

First, before forming the copper wiring **15**, the lower wiring **13** (see FIG. **3**) is formed on the semiconductor substrate **12** (see FIG. **3**) according to a well-known multilayer wiring manufacturing technique, and then the passivation film **14** is formed, and the via **24** that penetrates this passivation film **14** is formed.

Thereafter, as shown in FIG. **11**A, the barrier film **26** and the copper seed film **32** are formed on the surface of the passivation film **14** in this order, for example, according to the sputtering method.

Thereafter, as shown in FIG. **11**B, the resist film **33** selectively having an opening in a region in which each copper wiring **15** is to be formed is formed on the copper seed film **32**. Thereafter, copper is subjected to plating growth by means of electrolytic plating from the surface of the copper seed film **32** selectively exposed from the opening. As a result, the copper wiring **15** is formed. In this state, the copper wiring **15** has its side surface **28** covered with the resist film **33**. Additionally, adjacent copper wirings **15** are in a mutually electrically connected state through the copper seed film **32** covered with the resist film **33**.

Thereafter, as shown in FIG. **11**C, a Pd catalyst **47** is given to the upper surface **27** of the copper wiring **15** selectively exposed from the opening of the resist film **33** in a temperature environment of room temperature (about 20° C. or 25° C.)

Thereafter, as shown in FIG. **11**D, the resist film **33** is removed. As a result, the side surface **28** of the copper wiring **15** covered with the resist film **33** and the upper surface **27** to which the Pd catalyst **47** has been given are exposed. Thereafter, Ni is subjected to plating growth from the upper surface **27** of the copper wiring **15** by means of electroless plating.

At this time, the Pd catalyst **47** is not given to the side surface **28** of the copper wiring **15** covered with the resist film **33** when the Pd catalyst **47** is given, and therefore Ni hardly develops plating growth. As a result, Ni isotropically grows from the upper surface **27** of the copper wiring **15**, and the Ni film **44** selectively covering only the upper surface **27** of the copper wiring **15** is formed.

Thereafter, as shown in FIG. **11**E, the copper seed film **32** other than the copper wiring **15** and the barrier film **26** disposed thereunder are selectively removed, for example, according to wet etching. At this time, the end of the barrier film **26** is etched more inwardly than the side surface **28** of the copper wiring **15** because of characteristics of wet etching (isotropic etching), and a level difference is created between the end of the barrier film **26** and the side surface **28**.

Thereafter, as shown in FIG. **11**F, Pd and Au are subjected to plating growth in this order by means of electroless plating from the entire surface (side surface **28**) of the exposed copper wiring **15** and from the entire surface of the Ni film **44**. As a result, the Pd film **45** and the Au film **46** are formed.

The copper wiring **15** coated with the stacked films **44** to **46** consisting of the Ni film **44**, the Pd film **45**, and the Au film **46** is formed through the steps mentioned above.

As described above, according to the present embodiment, the Pd catalyst **47** is selectively given only to the upper surface **27** of the copper wiring **15** before forming the Ni film **44** (see FIG. **11**C). This makes it possible to restrain the plating growth of Ni from the side surface **28** of the copper wiring **15** when the Ni film **44** is subjected to electroless plating. As a result, the protection film (the Pd film **45** and the Au film **46**) covering the side surface **28** of the copper wiring **15** can be made thinner than in a case in which Ni, Pd, and Au are evenly grown by electroless plating from the upper surface **27** and the side surface **28** of the bare copper wiring **15**.

As a result, the distance between the stacked films **45** and **46** of adjacent copper wirings **15** can be secured comparatively widely, and therefore the occurrence of a wiring-to-

wiring short circuit can be prevented even if the wiring-to-wiring distance L of the copper wiring **15** is shortened. Additionally, the copper wiring **15** is completely covered with the stacked films **44** to **46** consisting of the Ni film **44**, the Pd film **45**, and the Au film **46**, and its surface is not exposed, and therefore the copper wiring **15** can be restrained from being oxidized or corroded.

Additionally, all platings can be treated by electroless plating after giving the Pd catalyst **47**. Electroless plating is bathtub type plating unlike one-by-one type electrolytic plating, and wafers can be treated at a time even if the wafers differ from each other in size. Therefore, the productivity of the semiconductor device **1** can be improved. Additionally, this electroless plating is performed after removing the resist film **33**, and therefore it is also possible to avoid the fact that the resist film **33** is deformed by being influenced by the plating temperature (about 90° C.) of electroless plating.

In the third embodiment, it is also possible to apply an example in which the Au film **46** is excluded in the same way as in the modification of FIG. **6** of the first embodiment.

<Fourth Embodiment>

FIG. **12** is a view showing a fourth embodiment of the copper wiring **15**. In FIG. **12**, only the copper wiring **15** and regions therearound are shown, and the structure etc., of the semiconductor chip **2** are neither shown nor described. Additionally, in FIG. **12**, the same reference sign is given to a component equivalent to each component of FIG. **3** shown above, and a description of this component is omitted.

In this fourth embodiment, the copper wiring **15** has a projecting portion **48** that projects outwardly at the lower end of its side surface **28**. The projecting portion **48** is formed by being drawn out toward both sides in a width direction of the copper wiring **15** with a predetermined thickness.

Additionally, an Ni (nickel) film **49** that is one example of the shock absorbing layer of the present invention, a Pd (palladium) film **50** that is one example of the bonding layer of the present invention, and an Au (gold) film **51** are stacked together in this order from the copper wiring **15** in such a way as to cover each copper wiring **15**.

The Ni film **49** is formed on the upper surface **27** of the copper wiring **15** with a uniform thickness such that its side surface becomes flush with the side surface **28** of the copper wiring **15**. In other words, the Ni film **49** is selectively formed only at the upper surface **27** so as to expose the side surface **28** of the copper wiring **15**. The thickness of the Ni film **49** is, for example, 2 μm to 4 μm.

The Pd film **50** is formed such that its one surface and its other surface follow the surface of the copper wiring **15** and the surface of the Ni film **49**, and covers the upper surface and the side surface of the Ni film **49** and covers the side surface **28** of the copper wiring **15** exposed from the Ni film **49**. The Pd film **50** is formed with a uniform thickness. The thickness of the Pd film **50** is, for example, 0.1 μm to 0.5 μm.

The Au film **51** is formed such that its one surface and its other surface follow the surface of the copper wiring **15** and the surface of the Ni film **49**, and covers the upper surface and the side surface of the Pd film **50**. The Au film **51** is formed with a uniform thickness that is thinner than the Pd film **50**. The thickness of the Au film **51** is, for example, 0 μm to 0.05 μm.

The Pd film **50** and the Au film **51** cover the side surface **28** from the upper end of the copper wiring **15** to the projecting portion **48** so as to selectively expose the side surface of the projecting portion **48**. Near the projecting portion **48**, the Pd film **50** and the Au film **51** come around the surface of the projecting portion **48** from the side surface **28** such that the Pd film **50** follows the side surface **28** and the surface of the projecting portion **48**. As a result, a part that has come around the projecting portion **48** of the Pd film **50** is interposed between the surface of the projecting portion **48** and the Au film **51**.

These stacked films **50** and **51** consisting of the Pd film **50** and the Au film **51** protect the side surface **28** of the copper wiring **15** by covering the side surface **28** as one example of the side protecting layer of the present invention. Additionally, the Ni film **49** is not formed at the side surface **28** in these stacked films **50** and **51**, and therefore a part on the side surface **28** of the copper wiring **15** is thinner than the distance from the upper surface **27** of the copper wiring **15** to the wire connection surface **35** (upper surface of the Au film **51**) of the copper wire **5** in the stacked films **50** and **51**.

In the present embodiment, the copper wiring **15** coated with the Ni film **49**, with the Pd film **50**, and with the Au film **51** is exposed to the surface of the semiconductor chip **2** in the form of the pad **7**. The copper wire **5** is bonded to the Au film **51** exposed to the topmost surface of the pad **7**.

Next, a process for manufacturing the copper wiring **15** of the fourth embodiment will be described.

FIG. **13**A to FIG. **13**F are views to describe a part of the manufacturing process of the copper wiring **15** of FIG. **12** in order of process steps. In the following description, let it be supposed that electrolytic plating is performed in a temperature environment of, for example, room temperature (about 20° C. or 25° C.) and that electroless plating is performed in a plating solution of, for example, about 90° C.

First, before forming the copper wiring **15**, the lower wiring **13** (see FIG. **3**) is formed on the semiconductor substrate **12** (see FIG. **3**) according to a well-known multi-layer wiring manufacturing technique, and then the passivation film **14** is formed, and the via **24** that penetrates this passivation film **14** is formed.

Thereafter, as shown in FIG. **13**A, the barrier film **26** and the copper seed film **32** are formed on the surface of the passivation film **14** in this order, for example, according to the sputtering method.

Thereafter, as shown in FIG. **13**B, the resist film **33** selectively having an opening in a region in which each copper wiring **15** is to be formed is formed on the copper seed film **32**. Thereafter, copper is subjected to plating growth by means of electrolytic plating from the surface of the copper seed film **32** selectively exposed from the opening. As a result, the copper wiring **15** is formed. In this state, the copper wiring **15** has its side surface **28** covered with the resist film **33**. Additionally, adjacent copper wirings **15** are in a mutually electrically connected state through the copper seed film **32** covered with the resist film **33**.

Thereafter, as shown in FIG. **13**C, Ni is subjected to plating growth by means of electrolytic plating from the upper surface **27** of the copper wiring **15** selectively exposed from the opening of the resist film **33**. As a result, the Ni film **49** (e.g., about 3 μm in thickness) brought into a sandwiched state from both sides by means of the resist film **33** is formed on the upper surface **27** of the copper wiring **15**.

Thereafter, as shown in FIG. **13**D, the resist film **33** is selectively etched so as to create a gap **52** between the resist film **33** and the side surface **28** of the copper wiring **15**. As a result, the side surface **28** of the copper wiring **15** and apart of the surface of the copper seed film **32** are exposed in the gap **52**. Such light etching as to allow the resist film **33** to be etched about 0.2 μm from the side surface **28** of the copper wiring **15**, for example, by supplying a dilute-sulfuric-acid etchant is applicable as an etching technique.

Preferably, at this time, the concentration and temperature of the dilute-sulfuric-acid etchant are kept constant.

Thereafter, as shown in FIG. **13**E, Pd and Au are subjected to plating growth in this order by means of electrolytic plating from the entire surface (side surface **28**) of the exposed copper wiring **15** and from the entire surface of the Ni film **49**. As a result, the Pd film **50** and the Au film **51** are formed. In this case, Pd and Au grow also from the surface of the copper seed film **32** exposed to the gap **52**.

Thereafter, as shown in FIG. **13**F, the resist film **33** is removed. Thereafter, the copper seed film **32** outside the Au film **51** and the barrier film **26** disposed thereunder are selectively removed, for example, according to wet etching. At this time, the end of the barrier film **26** is etched more inwardly than the side surface **28** of the copper wiring **15** because of characteristics of wet etching (isotropic etching), and a level difference is created between the end of the barrier film **26** and the side surface **28**.

The copper wiring **15** coated with the stacked films **49** to **51** consisting of the Ni film **49**, the Pd film **50**, and the Au film **51** is formed through the steps mentioned above.

As described above, according to the present embodiment, the Ni film **49** is formed only at the upper surface **27** of the copper wiring **15**, and the amount of plating growth can be allowed to fall within the range of the gap **52** of the resist film **33** during the plating of the Pd film **50** and the Au film **51**. Therefore, the protection film (the Pa film **50** and the Au film **51**) covering the side surface **28** of the copper wiring **15** can be made thinner than in a case in which Ni, Pd, and Au are evenly grown by electroless plating from the upper surface **27** and the side surface **28** of the bare copper wiring **15**. Additionally, the resist film **33** is interposed between adjacent copper wirings **15** during the plating of the Pd film **50** and the Au film **51** (see FIG. **13**E), and therefore Pd and Au that have grown never come into contact with each other.

As a result, the distance between the stacked films **50** and **51** of adjacent copper wirings **15** can be secured comparatively widely, and therefore the occurrence of a wiring-to-wiring short circuit can be prevented even if the wiring-to-wiring distance L of the copper wiring **15** is shortened. Additionally, the copper wiring **15** is completely covered with the stacked films **49** to **51** consisting of the Ni film **49**, the Pd film **50**, and the Au film **51**, and its surface is not exposed, and therefore the copper wiring **15** can be restrained from being oxidized or corroded.

In the fourth embodiment, it is also possible to apply an example in which the Au film **51** is excluded in the same way as in the modification of FIG. **6** of the first embodiment. Additionally, Ni may be subjected to plating growth prior to the Pd film **50** and the Au film **51** after creating the gap **52** in the resist film **33**.

<Reference Example>

FIG. **14** is a view showing a reference example of the copper wiring **15**. In FIG. **14**, only the copper wiring **15** and regions therearound are shown, and the structure etc., of the semiconductor chip **2** are neither shown nor described. Additionally, in FIG. **14**, the same reference sign is given to a component equivalent to each component of FIG. **3** shown above, and a description of this component is omitted.

In this reference example, each copper wiring **15** has an integrally-formed copper seed film **62** drawn outwardly at the lower end of the side surface **28**. The copper seed film **62** is a drawn portion formed by drawing both sides in the width direction of the copper wiring **15** while having a constant thickness.

A pedestal film **64** that is one example of a second insulating layer is formed on the copper seed film **62**. The pedestal film **64** exposes most of the upper and side surfaces **27** and **28** of the copper wiring **15**, and selectively surrounds and covers the lower part of the side surface **28** of the copper wiring **15**. The lower part of the copper wiring **15** is brought into a sandwiched state by means of the pedestal film **64** from both sides in the width direction when viewed cross-sectionally. The pedestal film **64** is formed with a uniform thickness. The thickness of the pedestal film **64** is, for example, 0.04 μm to 0.5 μm. The pedestal film **64** is made of the same material (SiN) as the passivation film **14**.

The barrier film **26** is formed such that its both ends are located inside the side surface of the pedestal film along with the copper seed film **62** when viewed cross-sectionally.

In each copper wiring **15**, an Ni (nickel) film **59** that is one example of the shock absorbing layer, a Pd (palladium) film **60** that is one example of the bonding layer, and an Au (gold) film **61** are stacked together in this order from the copper wiring **15** in such a way as to cover a part exposed from the pedestal film **64**. The stacked films **59** to **61** have a stacked-layer interface that intersects the surface of the pedestal film **64**. In other words, the pedestal film **64** has a shape formed by being drawn from the side surface **28** of the copper wiring **15** along a direction crossing the stacked-layer interface of the stacked films **59** to **61** when viewed cross-sectionally.

The Ni film **59** is formed such that its one surface and its other surface follow the upper surface **27** and the side surface **28** of the copper wiring **15**, and covers the whole area of the upper surface **27** and the side surface **28** exposed from the pedestal film **64**. The Ni film **59** is formed with a uniform thickness. The thickness of the Ni film **59** is, for example, 2 μm to 4 μm.

The Pd film **60** is formed such that its one surface and its other surface follow the upper surface **27** and the side surface **28** of the copper wiring **15**, and covers the whole area of the upper surface and the side surface of the Ni film **59**. The Pd film **60** is formed with a uniform thickness that is thinner than the Ni film **59**. The thickness of the Pd film **60** is, for example, 0.1 μm to 0.5 μm.

The Au film **61** is formed such that its one surface and its other surface follow the upper surface **27** and the side surface **28** of the copper wiring **15**, and covers the whole area of the upper surface and the side surface of the Pd film **60**. The Au film **61** is formed with a uniform thickness that is thinner than the Pd film **60**. The thickness of the Au film **61** is, for example, 0 μm to 0.05 μm.

These stacked films **59** to **61** consisting of the Ni film **59**, the Pd film **60**, and the Au film **61** protect the upper surface **27** and the side surface **28** of the copper wiring **15** by covering the upper surface **27** and the side surface **28** as one example of a protective layer. In this reference example, the copper wiring **15** coated with the Ni film **59**, with the Pd film **60**, and with the Au film **61** is exposed to the surface of the semiconductor chip **2** in the form of the pad **7**. The copper wire **5** is bonded to the Au film **61** exposed to the topmost surface of the pad **7**.

Next, a process for manufacturing the copper wiring **15** will be described.

FIG. **15**A to FIG. **15**F are views to describe a part of the manufacturing process of the copper wiring **15** of FIG. **14** in order of process steps. In the following description, let it be supposed that electrolytic plating is performed in a temperature environment of, for example, room temperature (about 20° C. or 25° C.) and that electroless plating is performed in a plating solution of, for example, about 90° C.

First, before forming the copper wiring **15**, the lower wiring **13** (see FIG. **14**) is formed on the semiconductor substrate **12** (see FIG. **14**) according to a well-known

multilayer wiring manufacturing technique, and then the passivation film **14** is formed, and the via **24** that penetrates this passivation film **14** is formed.

Thereafter, as shown in FIG. **15**A, the barrier film **26** and the copper seed film **62** are formed on the surface of the passivation film **14** in this order, for example, according to the sputtering method. Thereafter, the pedestal film **64** is formed on the copper seed film **62**, for example, according to the CVD method.

Thereafter, as shown in FIG. **15**B, the resist film **63** selectively having an opening in a region in which each copper wiring **15** is to be formed is formed on the pedestal film **64**. Thereafter, the pedestal film **64** exposed from the opening of the resist film **63** is selectively removed according to dry etching (chlorofluorocarbon-based dry etching) that uses the resist film **63** as a mask. As a result, the copper seed film **62** is selectively exposed in the opening of the resist film **63**.

Thereafter, as shown in FIG. **15**C, copper is subjected to plating growth by means of electrolytic plating from the surface of the copper seed film **62** selectively exposed from the opening of the resist film **63**. As a result, the copper wiring **15** is formed. In this state, the copper wiring **15** has its side surface **28** covered with the resist film **63**.

Thereafter, as shown in FIG. **15**D, the resist film **63** is removed. As a result, the side surface **28** of the copper wiring **15** covered with the resist film **63** is exposed. Thereafter, Ni, Pd, and Au are subjected to plating growth in this order by means of electroless plating from the entire surface (the upper surface **27** and the side surface **28**) of the exposed copper wiring **15**. Ni, Pd, and Au isotropically develop plating growth along the surface of the pedestal film **64** with a uniform thickness because of electroless plating. As a result, the stacked films **59** to **61** consisting of the Ni film **59**, the Pd film **60**, and the Au film **61** are formed.

Thereafter, as shown in FIG. **15**E, the pedestal film **64** outside the stacked films **59** to **61** is selectively removed according to dry etching (chlorofluorocarbon-based dry etching) so as to leave a part between the stacked films **59** to **61** and the copper seed film **62**.

Thereafter, as shown in FIG. **15**F, parts other than the part disposed under the pedestal film **64** in the copper seed film **62** and the barrier film **26** are selectively removed, for example, according to wet etching. At this time, the end of the copper seed film **62** and the end of the barrier film **26** are etched more inwardly than the side surface of the pedestal film **64** because of characteristics of wet etching (isotropic etching), and a level difference is created between the side surface of the pedestal film **64** and the ends of the copper seed film **62** and the barrier film **26**.

The copper wiring **15** coated with the stacked films **59** to **61** consisting of the Ni film **59**, the Pd film **60**, and the Au film **61** is formed through the steps mentioned above.

As described above, according to the present reference example, the plating interface of the stacked films **59** to **61** consisting of the Ni film **59**, the Pd film **60**, and the Au film **61** is formed on the pedestal film **64** (see FIG. **15**D). This pedestal film **64** is a film formed on the copper seed film **62** before etching the copper seed film **62** and the barrier film **26**. Therefore, residues (etching residues such as Cu and Ti) generated when the copper seed film **62** and the barrier film **26** are etched do not exist on the surface of the pedestal film **64** on which the stacked films **59** to **61** develop plating growth. Therefore, metallic particles that nucleate such etching residues can be prevented from developing plating growth in regions other than the region in which the stacked films **59** to **61** are formed between adjacent copper wirings **15**. Even if a plating core exists between the adjacent copper wirings **15** because of some factor and even if metallic particles develop plating growth from the core, the metallic particles will be removed along with a needless part of the pedestal film **64** in the step of FIG. **15**E, and therefore the metallic particles will never become a leak path of a wiring-to-wiring short circuit. Additionally, even if etching residues are generated when the copper seed film **62** and the barrier film **26** are etched (see FIG. **15**F), grain growth will never be developed to such an extent that these residues become a leak path because a plating step is not performed thereafter. As a result, there are no metallic particles that become a leak path even if the wiring-to-wiring distance L of the copper wiring **15** is shortened, and therefore the occurrence of a wiring-to-wiring short circuit can be prevented.

Additionally, the copper wiring **15** is completely covered with the stacked films **59** to **61** consisting of the Ni film **59**, the Pd film **60**, and the Au film **61**, and its surface is not exposed, and therefore the copper wiring **15** can be restrained from being oxidized or corroded.

Additionally, in the present reference example, all of the Ni film **59**, the Pd film **60**, and the Au film **61** are treated by electroless plating. Electroless plating is bathtub type plating unlike one-by-one type electrolytic plating, and wafers can be treated at a time even if the wafers differ from each other in size. Therefore, the productivity of the semiconductor device **1** can be improved. Additionally, this electroless plating is performed after removing the resist film **63**, and therefore it is also possible to avoid the fact that the resist film **63** is deformed by being influenced by the plating temperature (about 90° C.) of electroless plating.

With regard to the copper wiring **15** of the reference example, a modification shown in FIG. **16** can also be applied.

In FIG. **16**, the Ni film **59** is selectively formed only on the surface **27** so as to expose the side surface **28** of the copper wiring **15**. In this case, the side surface **28** of the copper wiring **15** is covered with the stacked films **60** and **61** consisting of the Pd film **60** and the Au film **61**. This arrangement can be obtained by forming the copper wiring **15** in, for example, the step of FIG. **15**C, thereafter by forming the Ni film **59** while allowing Ni to develop plating growth by means of electrolytic plating, and by excluding the electroless plating of Ni in the step of FIG. **15**D. In other words, the Ni film **59** is formed by plating growth in the opening of the resist film **63**, and therefore its side surface becomes flush with the side surface **28** of the copper wiring **15** (there is no level difference).

Although the embodiments of the present invention and the reference example have been described as above, the present invention and the reference example can be embodied in still another mode.

For example, a gold wire can also be used instead of the copper wire **5**.

Additionally, although a case in which the lower wiring **13** has a two-layer structure has been mentioned as one example in the aforementioned embodiments and the reference example, the lower wiring **13** may be a single-layer structure, a three-layer structure, and a four- or more layer structure.

Additionally, in the reference example, adjacent copper wirings **15** are in a mutually electrically connected state through the copper seed film **62** covered with the resist film **63**, for example, in the plating step of FIG. **15**D. Therefore, the stacked films **59** to **61** consisting of the Ni film **59**, the Pd film **60**, and the Au film **61** can be grown by electrolytic plating with respect to all of the copper wirings **15** by use of

the copper seed film **62**. If electrolytic plating is employed, the plating of Ni, Pd, and Au can be performed by using one device. Additionally, the Au film **61** is not necessarily required, and can be excluded.

The embodiments of the present invention are merely specific examples used to clarify the technical contents of the present invention, and the present invention should not be understood as being limited to these examples, and the spirit and scope of the present invention are to be determined solely by the appended claims.

From the contents of the aforementioned embodiments, the following features can be extracted besides the invention recited in the appended claims.

(Item 1)

A method for manufacturing a semiconductor device including a step of forming a copper wiring for wire connection on an insulating layer, a step of forming a mask so as to expose an upper surface of the copper wiring and cover a side surface of the copper wiring, a step of forming a shock absorbing layer on the upper surface of the copper wiring by plating the exposed upper surface of the copper wiring with a metallic material with a hardness higher than copper, and a step of forming a bonding layer having a connection surface for a wire on the side surface of the copper wiring and on the shock absorbing layer by removing the mask and then by performing plating with a metallic material.

According to this method, the shock absorbing layer is selectively formed on the upper surface of the copper wiring in a state in which the side surface of the copper wiring is covered with the mask. This makes it possible to secure a shock absorbing layer having a film thickness necessary to absorb a shock caused when a bonding wire is bonded in a region on the upper surface of the copper wiring. As a result, in subsequent steps, it is only necessary to completely stop growing a material of the shock absorbing layer on the upper surface of the copper wiring, or it is only necessary to grow the material of the shock absorbing layer comparatively thinly. Therefore, the amount of plating growth from the side surface of the copper wiring can be reduced, and therefore the thickness of the layer on the side surface of the copper wiring can be thinned.

(Item 2)

The method for manufacturing a semiconductor device according to Item 1, wherein the step of forming the shock absorbing layer includes a step of performing electrolytic plating with the material of the shock absorbing layer, and the step of forming the bonding layer includes a step of performing electroless plating with the material of the bonding layer.

According to this method, the plating step while the copper wiring is covered with the mask is performed by electrolytic plating, and the step after the mask has been removed is performed by electroless plating, and therefore it is possible to avoid the fact that the mask is deformed by being influenced by the plating temperature of electroless plating.

On the other hand, electroless plating is bathtub type plating unlike one-by-one type electrolytic plating, and wafers can be treated at a time even if the wafers differ from each other in size. Therefore, the productivity of the semiconductor device can be improved by positively employing electroless plating in a situation in which the influence of the aforementioned plating temperature is not undergone even when electroless plating is performed.

(Item 3)

The method for manufacturing a semiconductor device according to Item 1 or Item 2, wherein the step of forming the bonding layer includes a step of performing plating with the material of the bonding layer so as to become contiguous to the side surface of the exposed copper wiring by removing the mask.

According to this method, the thickness of the layer formed on the side surface of the copper wiring can be made thinner in proportion to an extent resulting from the fact that the shock absorbing layer is not formed on the side surface of the copper wiring.

(Item 4)

The method for manufacturing a semiconductor device according to Item 1 or Item 2, wherein the step of forming the shock absorbing layer includes a step of further operating plating with the material of the shock absorbing layer from the side surface of the copper wiring and from a surface of the shock absorbing layer before forming the bonding layer.

(Item 5)

A method for manufacturing a semiconductor device including a step of forming a copper wiring for wire connection on an insulating layer, a step of forming a sidewall made of an insulating material so as to expose an upper surface of the copper wiring and cover a side surface of the copper wiring, a step of forming a shock absorbing layer on the upper surface of the copper wiring by performing plating with a metallic material with a hardness higher than copper from the exposed upper surface of the copper wiring, and a step of forming a bonding layer to which a wire is bonded on the shock absorbing layer by further performing plating with a metallic material on the shock absorbing layer.

According to this method, the sidewall covering the side surface of the copper wiring is formed before forming the shock absorbing layer and the bonding layer. Therefore, when the plating of the shock absorbing layer and the plating of the bonding layer are performed, the material of the shock absorbing layer and the material of the bonding layer can be prevented from developing plating growth from the side surface of the copper wiring. Therefore, the amount of plating growth from the side surface of the copper wiring can be reduced, and therefore the thickness of the layer formed on the side surface of the copper wiring can be made thinner.

(Item 6)

The method for manufacturing a semiconductor device according to Item 5, wherein the step of forming the shock absorbing layer and the step of forming the bonding layer both include a step of performing electroless plating.

According to this method, the productivity of the semiconductor device can be improved by forming both the shock absorbing layer and the bonding layer by means of electroless plating.

(Item 7)

The method for manufacturing a semiconductor device according to Item 5 or Item 6, wherein the sidewall is made of an SiN film.

(Item 8)

A method for manufacturing a semiconductor device including a step of forming a copper wiring for wire connection on an insulating layer, a step of forming a mask so as to expose an upper surface of the copper wiring and cover a side surface of the copper wiring, a step of removing the mask after applying a catalyst onto the exposed upper surface of the copper wiring, a step of selectively forming a shock absorbing layer on the catalyst by performing plating with a metallic material with a hardness higher than copper after removing the mask, and a step of forming a bonding layer having a connection surface for a wire on the side

surface of the copper wiring and on the shock absorbing layer by further performing plating with a metallic material after forming the shock absorbing layer.

According to this method, a catalyst is selectively given only to the upper surface of the copper wiring before forming the shock absorbing layer. This makes it possible to restrain the material of the shock absorbing layer from developing plating growth from the side surface of the copper wiring when the shock absorbing layer is plated. Therefore, the amount of plating growth from the side surface of the copper wiring can be reduced, and therefore the thickness of the layer formed on the side surface of the copper wiring can be made thinner.

(Item 9)

The method for manufacturing a semiconductor device according to Item 8, wherein the step of forming the shock absorbing layer and the step of forming the bonding layer both include a step of performing electroless plating.

According to this method, the productivity of the semiconductor device can be improved by forming both the shock absorbing layer and the bonding layer by means of electroless plating.

(Item 10)

A method for manufacturing a semiconductor device including a step of forming a copper wiring for wire connection on an insulating layer, a step of forming a mask so as expose an upper surface of the copper wiring and to cover a side surface of the copper wiring, a step of forming a shock absorbing layer on the upper surface of the copper wiring by performing plating with a metallic material with a hardness higher than copper from the exposed upper surface of the copper wiring, a step of forming a gap between the mask and the side surface of the copper wiring by selectively etching the mask, and a step of forming a bonding layer having a connection surface for a wire on the side surface of the copper wiring and on the shock absorbing layer by further performing plating with a metallic material after forming the gap.

According to this method, the amount of plating growth can be set to fall within the range of the gap of the mask when the bonding layer is plated. Therefore, the amount of plating growth from the side surface of the copper wiring can be reduced, and therefore the thickness of the layer formed on the side surface of the copper wiring can be made thinner.

(Item 11)

The method for manufacturing a semiconductor device according to Item 10, wherein the step of forming the shock absorbing layer and the step of forming the bonding layer both include a step of performing electrolytic plating.

According to this method, the problem of deformation of the mask can be avoided by performing the plating step during which the copper wiring is covered with the mask by means of electrolytic plating.

(Item 12)

The method for manufacturing a semiconductor device according to any one of Item 1 to Item 11, wherein the step of forming the shock absorbing layer includes a step of plating an Ni film.

(Item 13)

The method for manufacturing a semiconductor device according to any one of Item 1 to Item 12, wherein the step of forming the bonding layer includes a step of plating a Pd film and an Au film in this order.

(Item 14)

The method for manufacturing a semiconductor device according to any one of Item 1 to Item 13, further including a step of forming a barrier film between the insulating layer and the copper wiring.

Additionally, from the contents of the aforementioned reference example, the following features can be extracted.

(Item 1)

A semiconductor device including a first insulating layer, a copper wiring for wire connection formed on the first insulating layer, a second insulating layer surrounding the copper wiring and selectively covering a lower part of a side surface of the copper wiring, a copper seed layer disposed between the first insulating layer and the second insulating layer, the copper seed layer formed integrally with the copper wiring, and a protective layer made of a metallic material covering an upper surface and a side surface of the copper wiring on the second insulating layer.

This semiconductor device can be manufactured according to a method for manufacturing a semiconductor device recited in Item 10 mentioned below.

(Item 2)

The semiconductor device according to Item 1, wherein the protective layer includes a shock absorbing layer formed on the copper wiring, the shock absorbing layer being made of a metallic material with a hardness higher than copper and a bonding layer for a wire formed on the shock absorbing layer.

(Item 3)

The semiconductor device according to Item 2, wherein the protective layer has a stacked structure consisting of the shock absorbing layer and the bonding layer in a whole area thereof.

(Item 4)

The semiconductor device according to Item 2, wherein the protective layer has a stacked structure consisting of the shock absorbing layer and the bonding layer in a region on the upper surface of the copper wiring, and has the bonding layer contiguous to the side surface of the copper wiring in a region on the side surface of the copper wiring.

(Item 5)

The semiconductor device according to any one of Item 2 to Item 4, wherein the shock absorbing layer is made of an Ni film.

(Item 6)

The semiconductor device according to any one of Item 2 to Item 5, wherein the bonding layer includes a stacked structure consisting of a Pd film and an Au film that are stacked in this order from the shock absorbing layer.

(Item 7)

The semiconductor device according to any one of Item 1 to Item 6, wherein the first insulating layer and the second insulating layer are both made of an SiN film.

(Item 8)

The semiconductor device according to any one of Item 1 to Item 7, further including a barrier film interposed between the first insulating layer and the copper wiring.

(Item 9)

The semiconductor device according to any one of Item 1 to Item 8, wherein a plurality of copper wirings each of which is the copper wiring are formed at a wiring-to-wiring distance of less than 20 μm.

According to this arrangement, the wiring-to-wiring distance is less than 20 μm, and therefore the wiring can be greatly reduced in size.

(Item 10)

A method for manufacturing a semiconductor device including a step of forming a copper seed layer on a first insulating layer, a step of forming a second insulating layer having an opening that selectively exposes an upper surface of the copper seed layer, a step of forming a copper wiring for wire connection so as to protrude from the second insulating layer by plating the exposed upper surface of the copper seed layer with copper, a step of forming a protective layer covering an upper surface and a side surface of the copper wiring by plating the copper wiring exposed from the second insulating layer with a metallic material, and a step of exposing the first insulating layer by selectively removing a part of the second insulating layer exposed from the protective layer and by selectively removing the copper seed layer directly thereunder.

According to this method, a plating interface of the protective layer is formed between the second insulating layer and the protective layer. This second insulating layer is a layer formed on the copper seed layer. For example, etching residues of the copper seed layer or etching residues a barrier film which is formed between the copper seed layer and the first insulating layer do not exist on the second insulating layer. Therefore, metallic particles that nucleate these etching residues can be prevented from developing plating growth at a part other than the protective layer. As a result, there are no metallic particles that become a leak path even if the wiring-to-wiring distance of the copper wiring is shortened, and therefore the occurrence of a wiring-to-wiring short circuit can be prevented.

Additionally, the copper wiring is completely covered with the protective layer, and its surface is not exposed, and therefore the copper wiring can be restrained from being oxidized or corroded.

(Item 11)

The method for manufacturing a semiconductor device according to Item 10, wherein the step of forming the protective layer includes a step of forming a shock absorbing layer on the copper wiring by performing plating with a metallic material with a hardness higher than copper and a step of forming the bonding layer for a wire on the shock absorbing layer.

The semiconductor device according to Item 2 extracted from the reference example can be manufactured by this method.

Additionally, the protective layer can be formed by forming the shock absorbing layer and the bonding layer, and therefore the manufacturing process can be simplified.

(Item 12)

The method for manufacturing a semiconductor device according to Item 11, wherein the step of forming the shock absorbing layer includes a step of forming the shock absorbing layer on an entire surface of the copper wiring exposed from the second insulating layer, and the step of forming the bonding layer includes a step of forming the bonding layer on an entire surface of the shock absorbing layer.

The semiconductor device according to Item 3 extracted from the reference example can be manufactured by this method.

Additionally, the plating of the entire surface of the shock absorbing layer and the plating of the entire surface of the bonding layer are employed, and therefore, for example, a step of selectively covering the surface of the copper wiring during plating formation can be excluded. Therefore, the manufacturing process can be made even simpler.

(Item 13)

The method for manufacturing a semiconductor device according to Item 11, wherein the step of forming the shock absorbing layer includes a step of selectively forming the shock absorbing layer on the upper surface of the copper wiring so that plating is not applied onto the side surface of the copper wiring, and the step of forming the bonding layer includes a step of forming the bonding layer so as to be contiguous to the side surface of the copper wiring.

The semiconductor device according to Item 4 extracted from the reference example can be manufactured by this method.

(Item 14)

The method for manufacturing a semiconductor device according to any one of Item 10 to Item 13, wherein the step of forming the protective layer includes a step of performing electroless plating with the metallic material.

Electroless plating is bathtub type plating unlike one-by-one type electrolytic plating, and wafers can be treated at a time even if the wafers differ from each other in size. Therefore, the productivity of the semiconductor device can be improved by employing electroless plating.

(Item 15)

The method for manufacturing a semiconductor device according to any one of Item 10 to Item 13, wherein the step of forming the protective layer includes a step of performing electrolytic plating with the metallic material.

The invention claimed is:

1. A semiconductor device comprising:
- a semiconductor chip including:
  - a semiconductor substrate;
  - a multilayer wiring structure disposed on the semiconductor substrate, the multilayer wiring structure including at least one insulating layer and at least one wiring layer;
  - a copper wiring for wire connection formed on the at least one insulating layer;
  - a shock absorbing layer formed on an upper surface of the copper wiring, the shock absorbing layer being made of a metallic material with a hardness higher than copper;
  - a bonding layer formed on the shock absorbing layer, the bonding layer having a connection surface;
  - a side protecting layer covering a side surface of the copper wiring from an upper end of the side surface to a lower end of the side surface, and
  - a barrier film interposed between the at least one insulating layer and the copper wiring;
- a first lead on which the semiconductor chip is mounted;
- a second lead separated from the first lead; and
- a bonding wire bonded to the connection surface of the bonding layer and the second lead, wherein
- the barrier film has an end surface positioned farther inside than the side surface of the copper wiring such that a level difference along a surface of the semiconductor substrate is formed between the end surface of the barrier film and the side surface of the copper wiring,
- the side protecting layer has a thickness thinner than a distance from the upper surface of the copper wiring to the connection surface of the bonding layer,
- a portion of the side protecting layer is disposed in the level difference while reaching the at least one insulating layer, and
- the at least one wiring layer is disposed directly beneath a connection portion of the connection surface to which the bonding wire is bonded.

2. The semiconductor device according to claim **1**, wherein the shock absorbing layer is selectively formed only on the upper surface of the copper wiring.

3. The semiconductor device according to claim **2**, wherein the bonding layer has a first portion covering the side surface of the copper wiring and a second portion covering an upper surface of the shock absorbing layer, and

the side protecting layer includes the first portion of the bonding layer.

4. The semiconductor device according to claim **3**, wherein the copper wiring has a projecting portion projecting outwardly at the lower end of the side surface, and

the side protecting layer covers the side surface of the copper wiring from an upper end of the copper wiring to the projecting portion.

5. The semiconductor device according to claim **2**, wherein the side protecting layer includes a sidewall made of an insulating material.

6. The semiconductor device according to claim **5**, wherein the sidewall is made of an SiN film.

7. The semiconductor device according to claim **3**, wherein the shock absorbing layer has a side surface flush with the side surface of the copper wiring.

8. The semiconductor device according to claim **3**, wherein the shock absorbing layer projects more sidewardly than the copper wiring such that a level difference is formed between a side surface of the shock absorbing layer and the side surface of the copper wiring.

9. The semiconductor device according to claim **1**, wherein the shock absorbing layer has a first portion covering the side surface of the copper wiring and a second portion covering the upper surface of the copper wiring, the first portion having a thickness thinner than a thickness of the second portion, and

the side protecting layer includes the first portion of the shock absorbing layer.

10. The semiconductor device according to claim **9**, wherein the bonding layer has a first portion covering the first portion of the shock absorbing layer and a second portion covering the second portion of the shock absorbing layer, and

the side protecting layer further includes the first portion of the bonding layer.

11. The semiconductor device according to claim **1**, wherein the shock absorbing layer is made of an Ni film.

12. The semiconductor device according to claim **1**, wherein the bonding layer includes a stacked structure consisting of a Pd film and an Au film stacked in that stated order from the shock absorbing layer.

13. The semiconductor device according to claim **1**, wherein the level difference is below the copper wiring.

14. The semiconductor device according to claim **1**, wherein the barrier film is made of Ti.

15. The semiconductor device according to claim **1**, wherein a plurality of copper wirings, each of which is the copper wiring, are formed at a wiring-to-wiring distance of less than 20 μm.

16. The semiconductor device according to claim **1**, wherein a part of the shock absorbing layer disposed on the upper surface of the copper wiring has a 2 μm to 4 μm thickness.

17. The semiconductor device according to claim **1**, wherein the at least one insulating layer includes a passivation film formed on a topmost surface of the multilayer wiring structure.

18. The semiconductor device according to claim **1**, wherein the side protecting layer completely covers the side surface of the copper wiring from an upper end of the copper wiring to a lower end of the copper wiring.

* * * * *